Memory Systems and Memory-Centric Computing Systems
Lecture 2, Topic 1: Memory Trends and Basics

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HiPEAC ACACES Summer School 2018

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Carnegie Mellon

What Will You Learn in This Course?

- Memory Systems and Memory-Centric Computing Systems
  - July 9-13, 2018

- Topic 1: Main Memory Trends and Basics
- Topic 2: Memory Reliability & Security: RowHammer and Beyond
- Topic 3: In-memory Computation
- Topic 4: Low-Latency and Low-Energy Memory
- Topic 5 (unlikely): Enabling and Exploiting Non-Volatile Memory
- Topic 6 (unlikely): Flash Memory and SSD Scaling

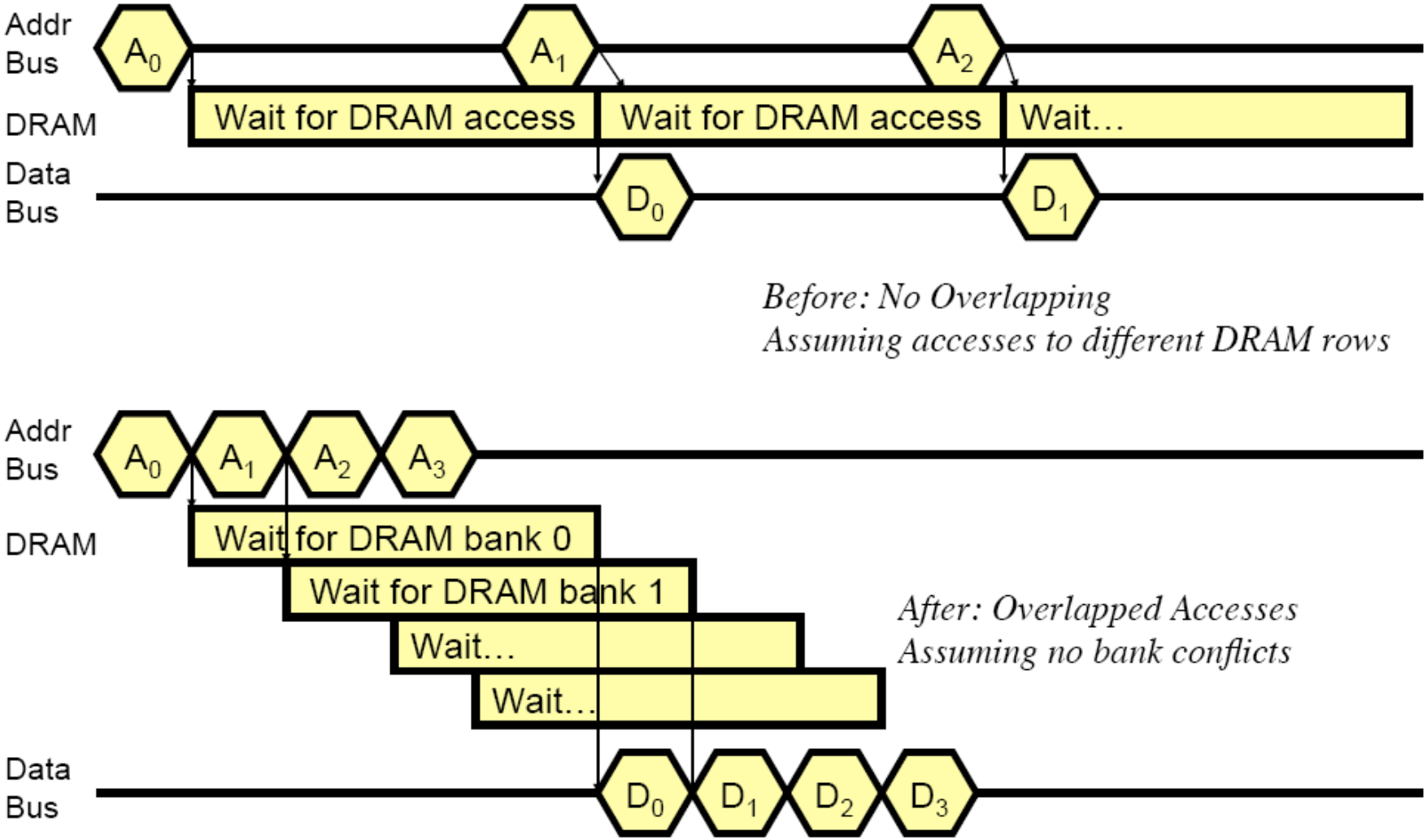
- Major Overview Reading:
  - Mutlu and Subramanian, "Research Problems and Opportunities in Memory Systems," SUPERFRI 2014.

Multiple Banks (Interleaving) and Channels

- Multiple banks
  - Enable concurrent DRAM accesses
  - Bits in address determine which bank an address resides in
- Multiple independent channels serve the same purpose
  - But they are even better because they have separate data buses
  - Increased bus bandwidth

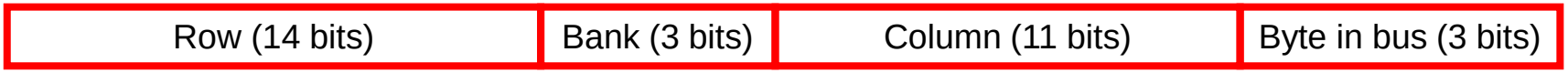
- Enabling more concurrency requires reducing
  - Bank conflicts
  - Channel conflicts
- How to select/randomize bank/channel indices in address?
  - Lower order bits have more entropy
  - Randomizing hash functions (XOR of different address bits)

How Multiple Banks Help

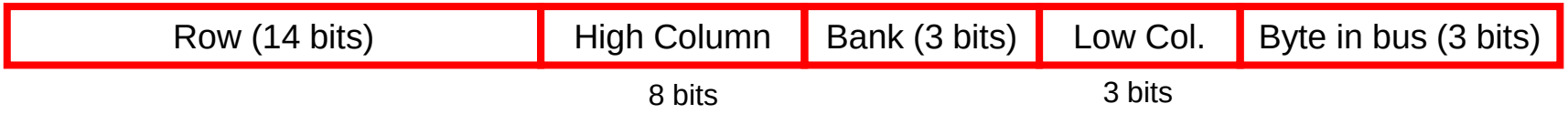


Address Mapping (Single Channel)

- Single-channel system with 8-byte memory bus
  - 2GB memory, 8 banks, 16K rows & 2K columns per bank
- Row interleaving
  - Consecutive rows of memory in consecutive banks



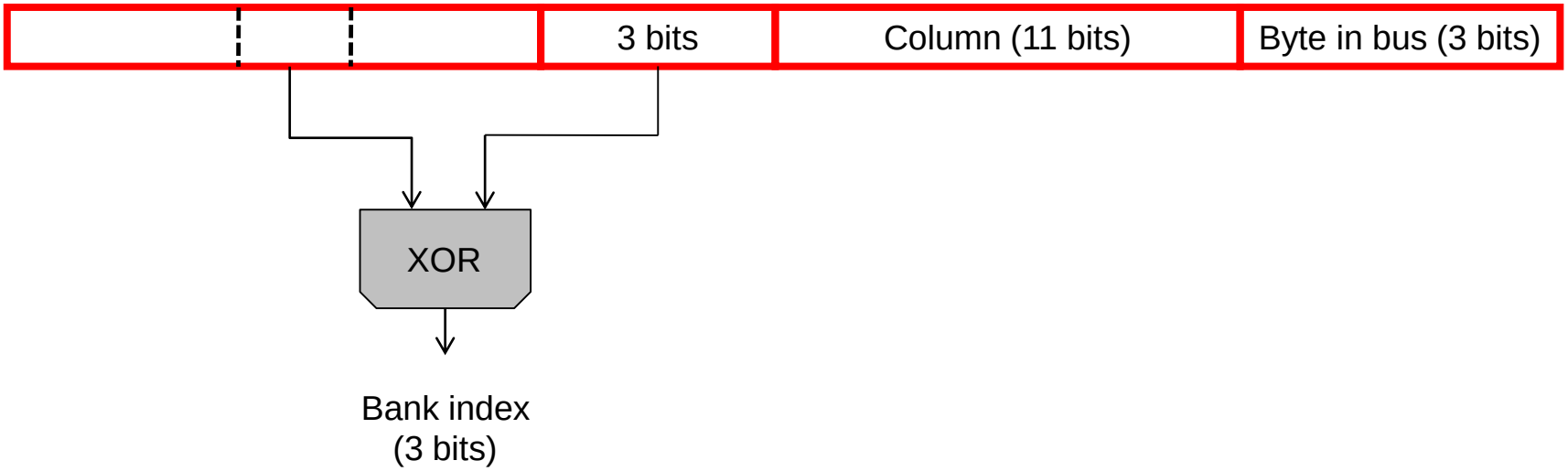
  - Accesses to consecutive cache blocks serviced in a pipelined manner
- Cache block interleaving
  - Consecutive cache block addresses in consecutive banks
  - 64 byte cache blocks



  - Accesses to consecutive cache blocks can be serviced in parallel

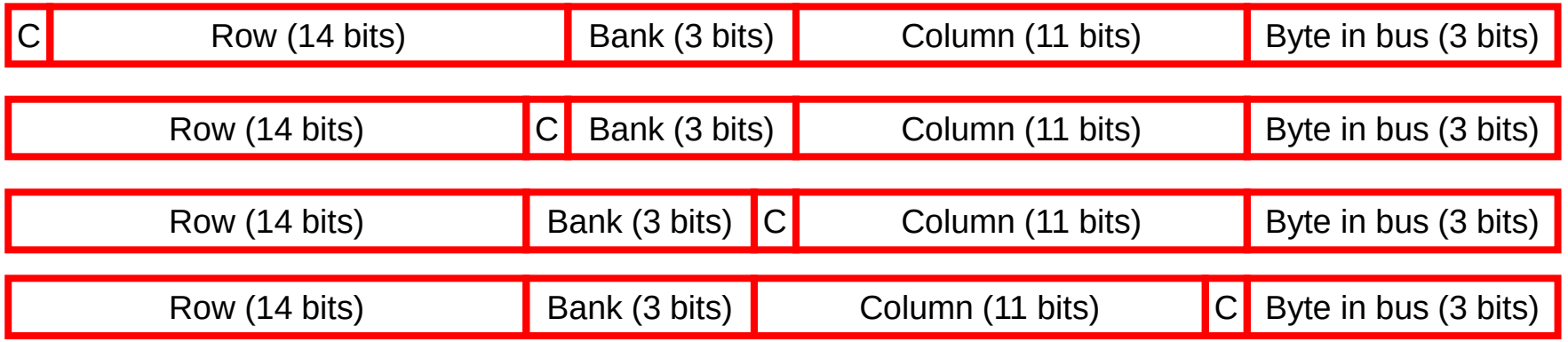
Bank Mapping Randomization

- DRAM controller can randomize the address mapping to banks so that bank conflicts are less likely

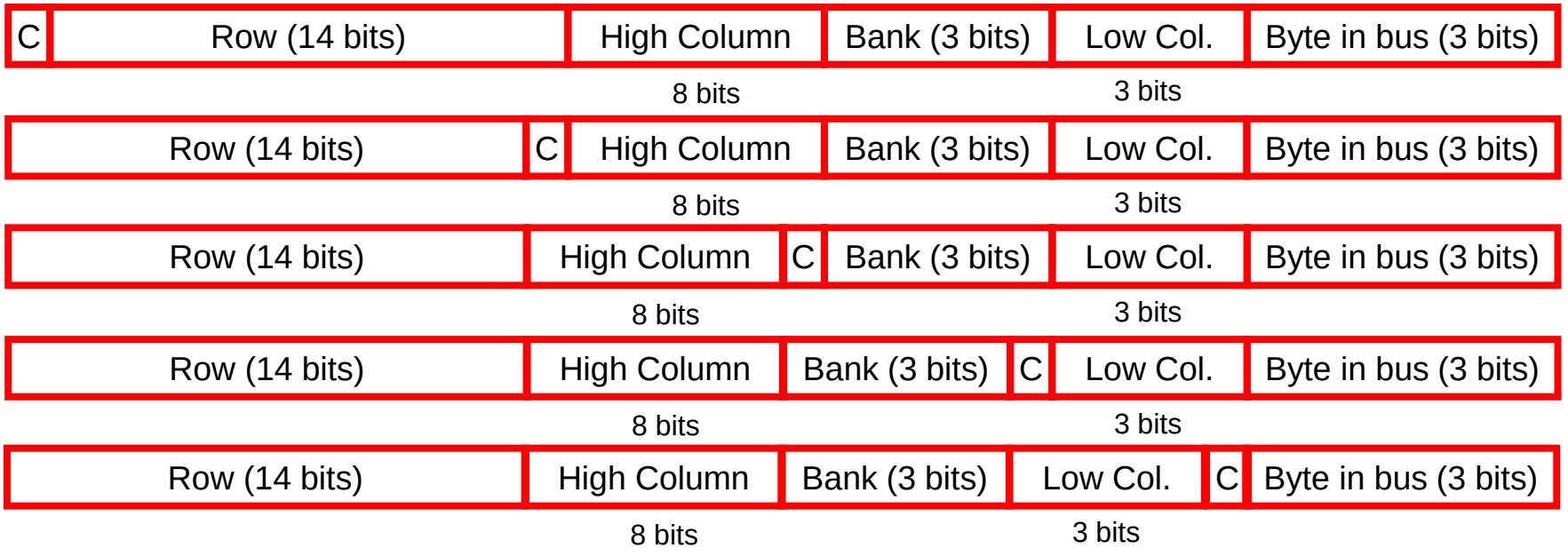


- Reading:
  - Rau, "Pseudo-randomly Interleaved Memory," ISCA 1991.

Address Mapping (Multiple Channels)

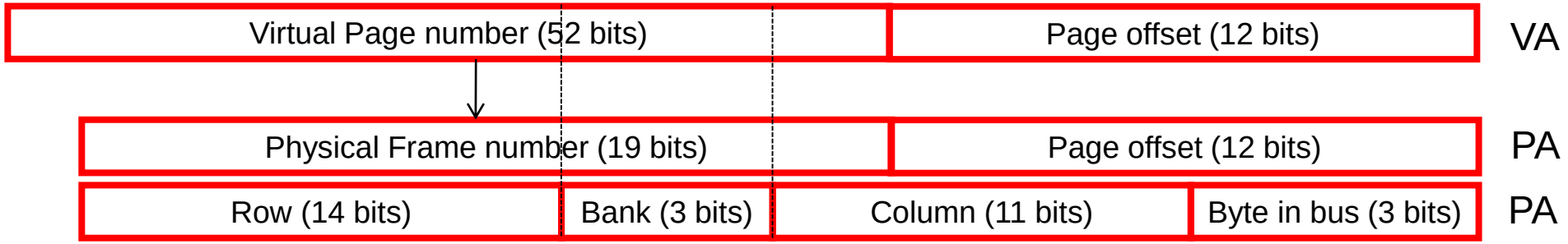


- Where are consecutive cache blocks?



Interaction with Virtual→Physical Mapping

- Operating System influences where an address maps to in DRAM



- Operating system can influence which bank/channel/rank a virtual page is mapped to.

- It can perform page coloring to
  - Minimize bank conflicts
  - Minimize inter-application interference **[Muralidhara+ MICRO'11]**
  - Minimize latency in the network **[Das+ HPCA'13]**

Memory Channel Partitioning

- Sai Prashanth Muralidhara, Lavanya Subramanian, Onur Mutlu, Mahmut Kandemir, and Thomas Moscibroda, **"Reducing Memory Interference in Multicore Systems via Application-Aware Memory Channel Partitioning"** *Proceedings of the 44th International Symposium on Microarchitecture (**MICRO**)*, Porto Alegre, Brazil, December 2011. Slides (pptx)

Reducing Memory Interference in Multicore Systems via Application-Aware Memory Channel Partitioning

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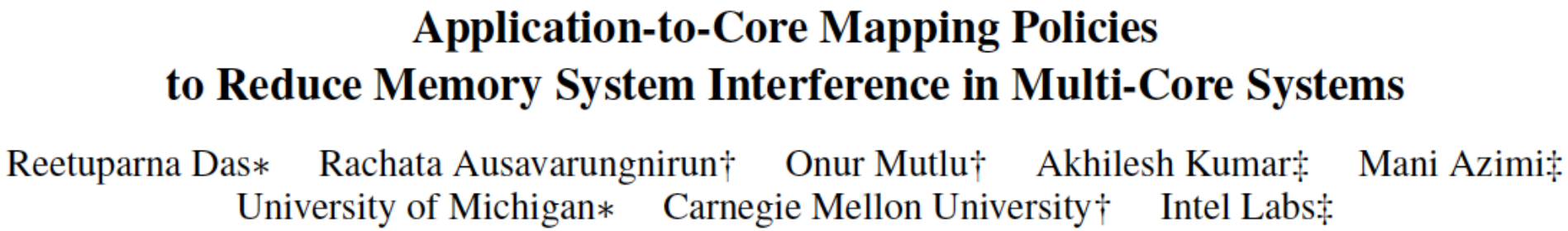
Application-to-Core Mapping

- Reetuparna Das, Rachata Ausavarungnirun, Onur Mutlu, Akhilesh Kumar, and Mani Azimi,
  "Application-to-Core Mapping Policies to Reduce Memory System Interference in Multi-Core Systems"
  *Proceedings of the 19th International Symposium on High-Performance Computer Architecture (**HPCA**)*, Shenzhen, China, February 2013.
  Slides (pptx)



Application-to-Core Mapping Policies to Reduce Memory System Interference in Multi-Core Systems

Reetuparna Das* Rachata Ausavarungnirun† Onur Mutlu† Akhilesh Kumar‡ Mani Azimi‡
University of Michigan* Carnegie Mellon University† Intel Labs‡

More on Reducing Bank Conflicts

- Read Sections 1 through 4 of:
  - Kim et al., "A Case for Exploiting Subarray-Level Parallelism in DRAM," ISCA 2012.

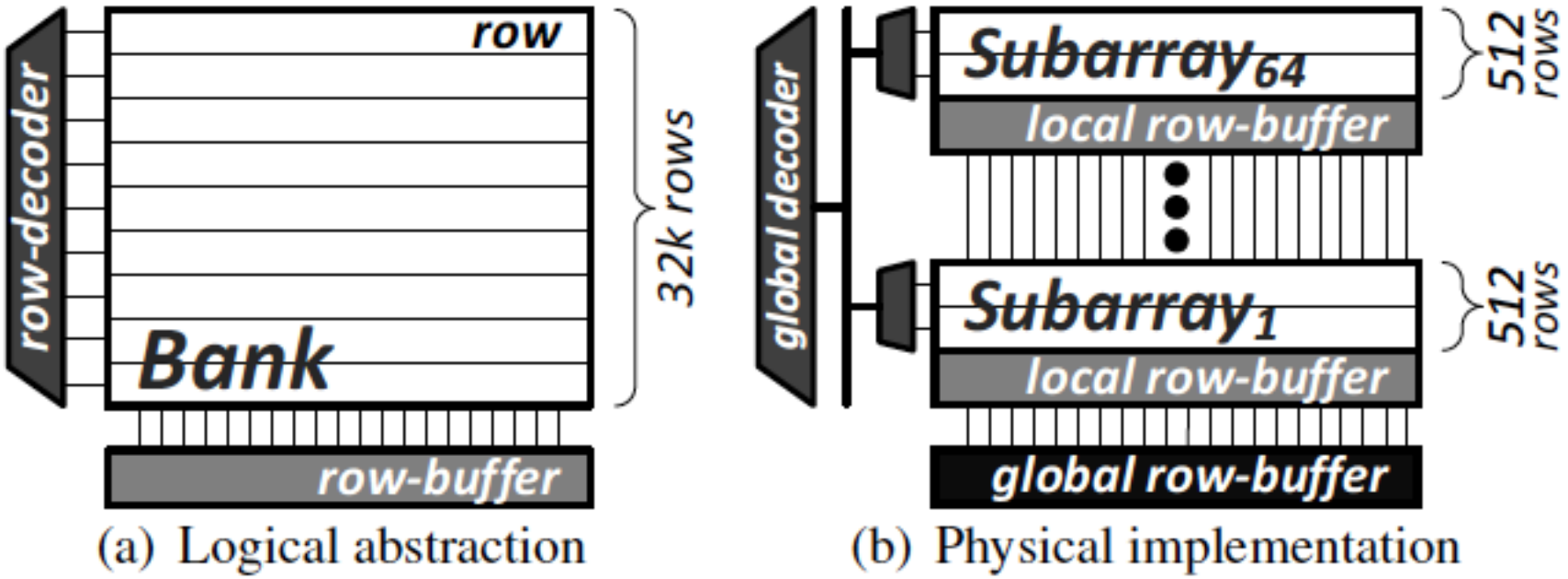


Figure 1. DRAM bank organization

Subarray Level Parallelism

- Yoongu Kim, Vivek Seshadri, Donghyuk Lee, Jamie Liu, and Onur Mutlu, **"A Case for Exploiting Subarray-Level Parallelism (SALP) in DRAM"**
  *Proceedings of the 39th International Symposium on Computer Architecture (**ISCA**)*, Portland, OR, June 2012. Slides (pptx)

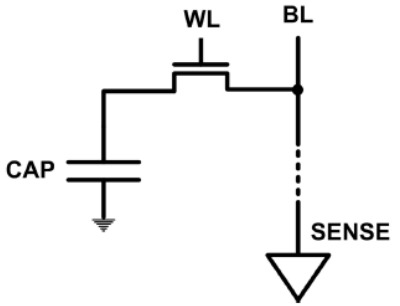
A Case for Exploiting Subarray-Level Parallelism (SALP) in DRAM

Yoongu Kim Vivek Seshadri Donghyuk Lee Jamie Liu Onur Mutlu

Carnegie Mellon University

DRAM Refresh (I)

- DRAM capacitor charge leaks over time
- The memory controller needs to read each row periodically to restore the charge
  - Activate + precharge each row every N ms
  - Typical N = 64 ms



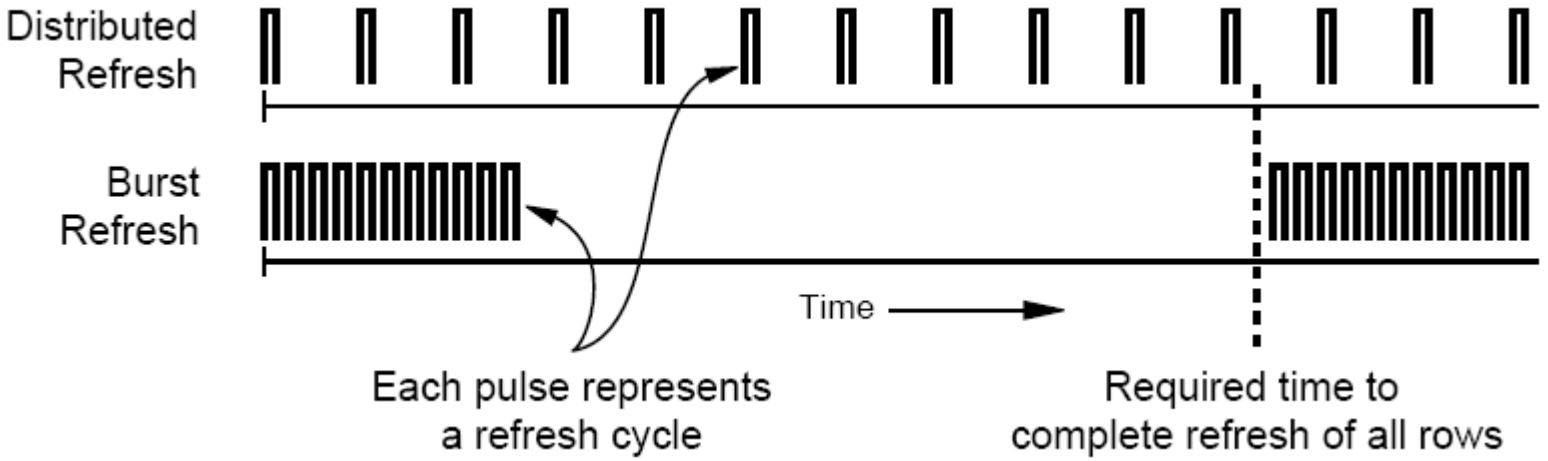
- Implications on performance?

  -- DRAM bank unavailable while refreshed

  -- Long pause times: If we refresh all rows in burst, every 64ms the DRAM will be unavailable until refresh ends

- Burst refresh: All rows refreshed immediately after one another
- Distributed refresh: Each row refreshed at a different time, at regular intervals

DRAM Refresh (II)



- Distributed refresh eliminates long pause times
- How else we can reduce the effect of refresh on performance?
  - Can we reduce the number of refreshes?

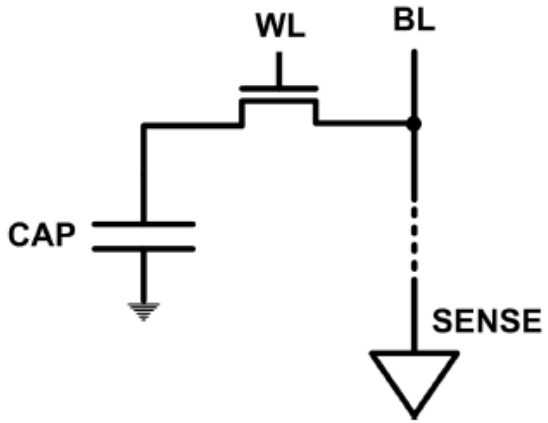
Downsides of DRAM Refresh

-- Energy consumption: Each refresh consumes energy

-- Performance degradation: DRAM rank/bank unavailable while refreshed

-- QoS/predictability impact: (Long) pause times during refresh

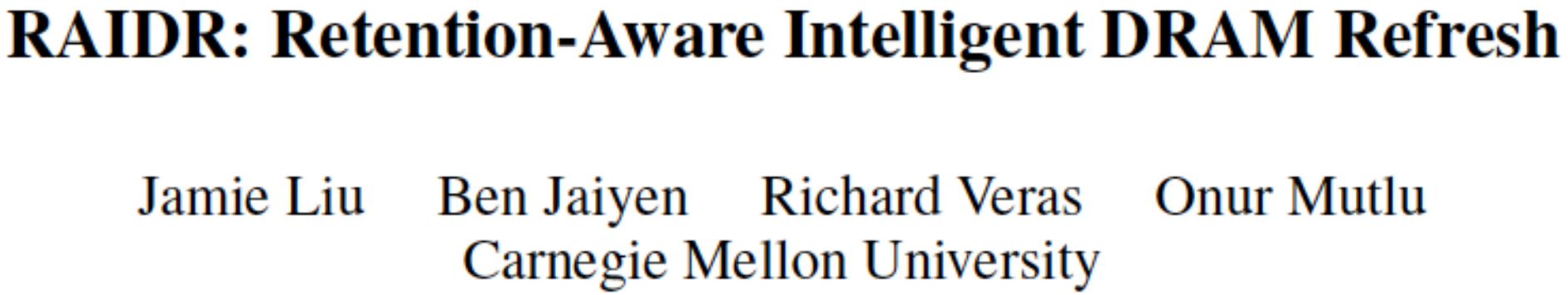
-- Refresh rate limits DRAM density scaling



Liu et al., "RAIDR: Retention-aware Intelligent DRAM Refresh," ISCA 2012.

More on DRAM Refresh

- Jamie Liu, Ben Jaiyen, Richard Veras, and Onur Mutlu, **"RAIDR: Retention-Aware Intelligent DRAM Refresh"** *Proceedings of the 39th International Symposium on Computer Architecture (**ISCA**)*, Portland, OR, June 2012. Slides (pdf)



DRAM Retention Analysis

- Jamie Liu, Ben Jaiyen, Yoongu Kim, Chris Wilkerson, and Onur Mutlu, **"An Experimental Study of Data Retention Behavior in Modern DRAM Devices: Implications for Retention Time Profiling Mechanisms"** *Proceedings of the 40th International Symposium on Computer Architecture (**ISCA**)*, Tel-Aviv, Israel, June 2013. Slides (ppt) Slides (pdf)

An Experimental Study of Data Retention Behavior in Modern DRAM Devices: Implications for Retention Time Profiling Mechanisms

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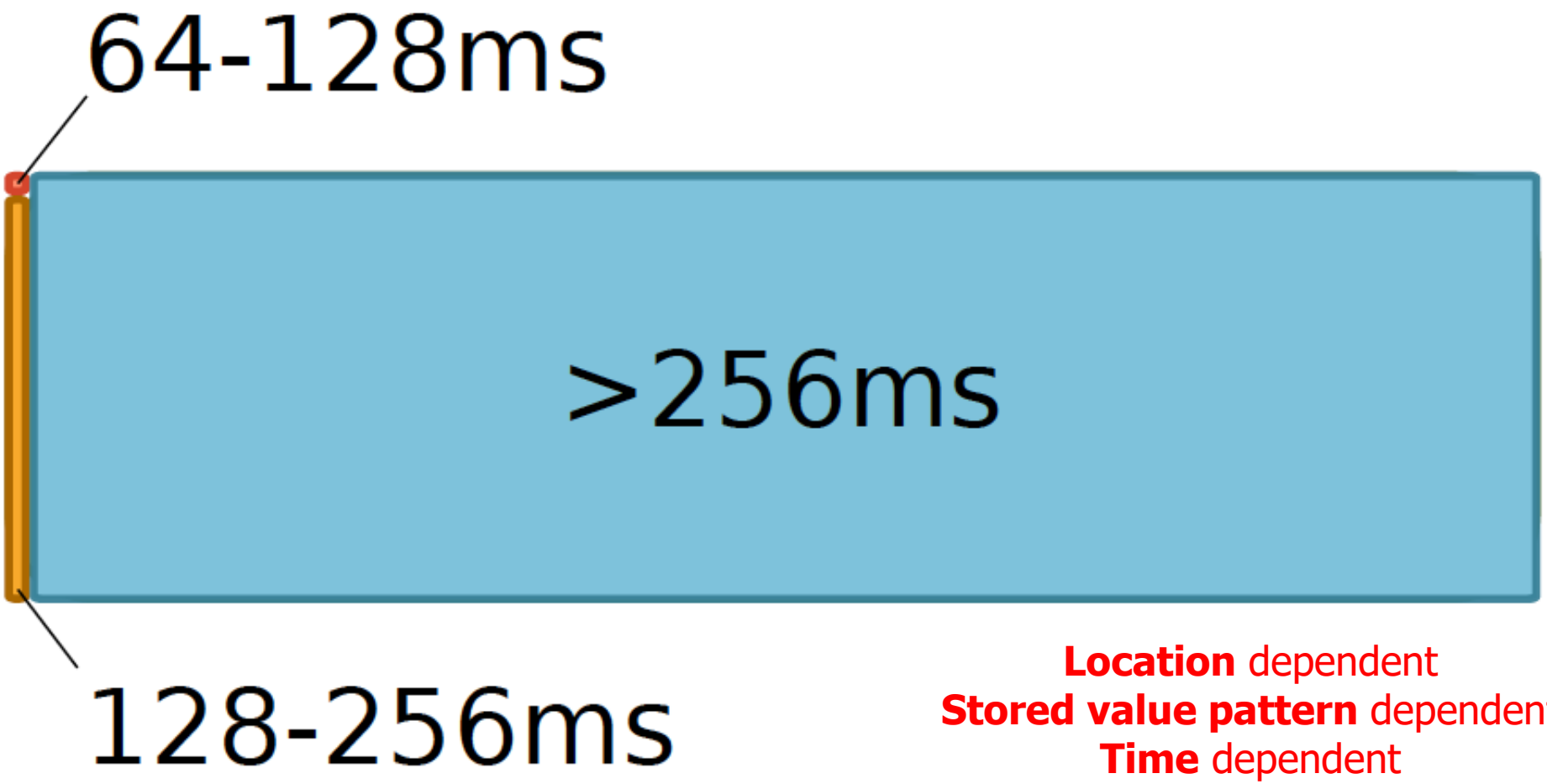
Data Retention in Memory [Liu et al., ISCA 2013]

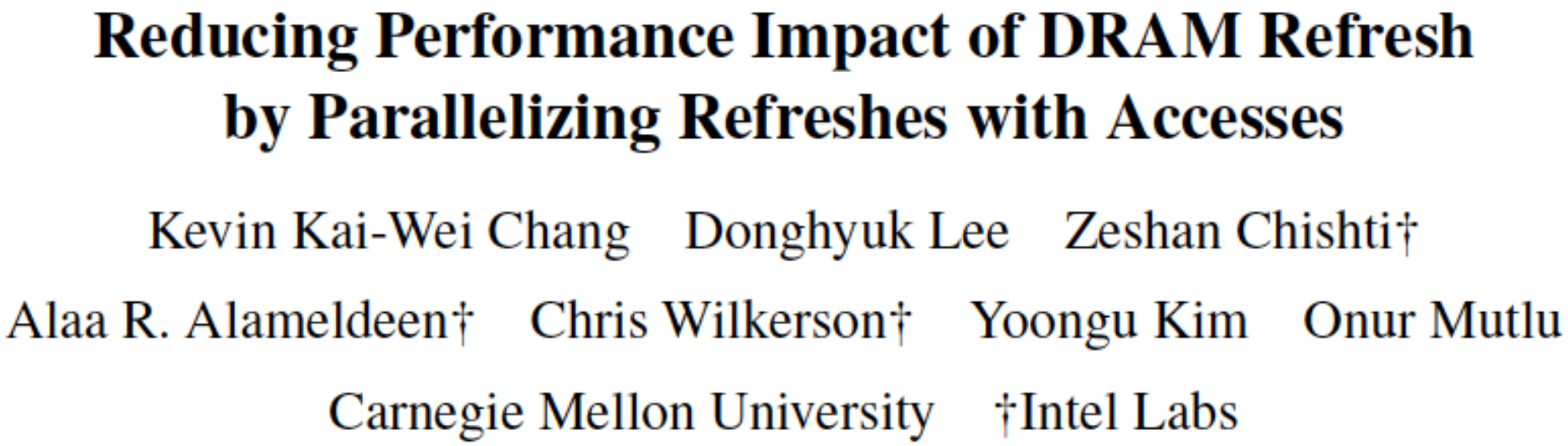
- Data Retention Time Profile of DRAM looks like this:



Location dependent
Stored value pattern dependent
Time dependent

DRAM Refresh-Access Parallelization

- Kevin Chang, Donghyuk Lee, Zeshan Chishti, Alaa Alameldeen, Chris Wilkerson, Yoongu Kim, and Onur Mutlu,
  "Improving DRAM Performance by Parallelizing Refreshes with Accesses"
  *Proceedings of the 20th International Symposium on High-Performance Computer Architecture (**HPCA**)*, Orlando, FL, February 2014.
  [Summary] [Slides (pptx) (pdf)]



Reducing Performance Impact of DRAM Refresh by Parallelizing Refreshes with Accesses

Kevin Kai-Wei Chang Donghyuk Lee Zeshan Chishti†

Alaa R. Alameldeen† Chris Wilkerson† Yoongu Kim Onur Mutlu

Carnegie Mellon University †Intel Labs

Memory Controllers

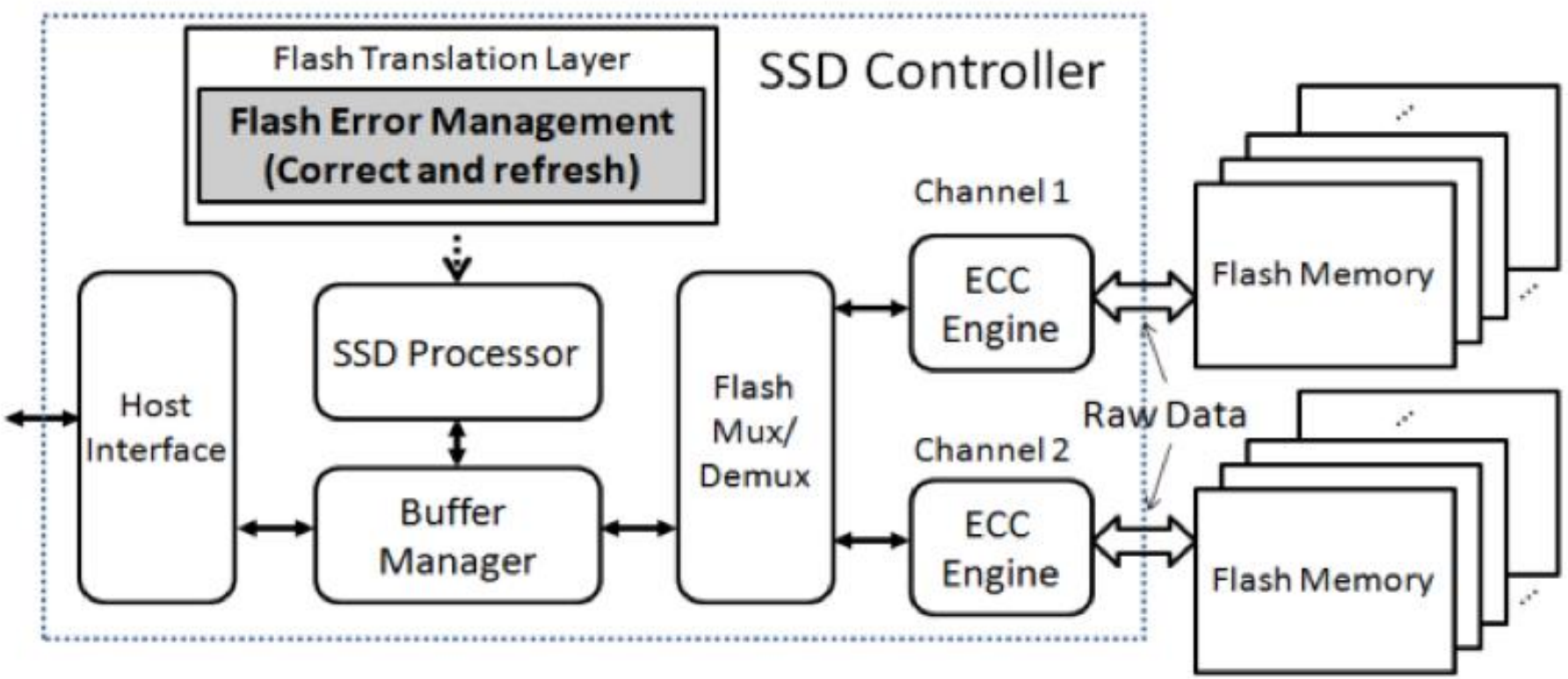
DRAM versus Other Types of Memories

- Long latency memories have similar characteristics that need to be controlled.

- The following discussion will use DRAM as an example, but many scheduling and control issues are similar in the design of controllers for other types of memories
  - Flash memory
  - Other emerging memory technologies
    - Phase Change Memory
    - Spin-Transfer Torque Magnetic Memory
  - These other technologies can place other demands on the controller

Flash Memory (SSD) Controllers

- Similar to DRAM memory controllers, except:
  - They are flash memory specific
  - They do much more: error correction, garbage collection, page remapping, …



Cai+, "Flash Correct-and-Refresh: Retention-Aware Error Management for Increased Flash Memory Lifetime", ICCD 2012.

Another View of the SSD Controller

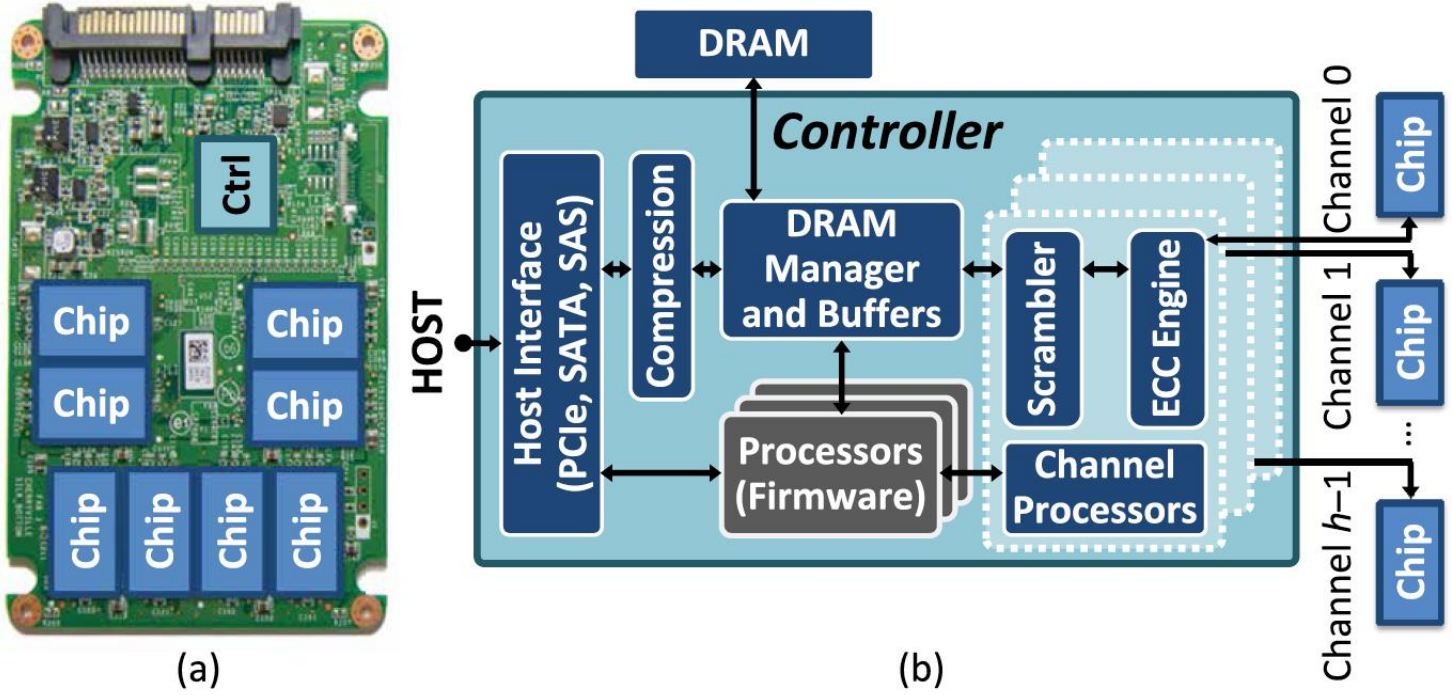


Fig. 1. ***(a) SSD system architecture, showing controller (Ctrl) and chips. (b) Detailed view of connections between controller components and chips.***

Cai+, "Error Characterization, Mitigation, and Recovery in Flash Memory Based Solid State Drives," Proc. IEEE 2017.

https://arxiv.org/pdf/1711.11427.pdf

On Modern SSD Controllers (I)

Proceedings of the IEEE, Sept. 2017

Error Characterization, Mitigation, and Recovery in Flash-Memory-Based Solid-State Drives

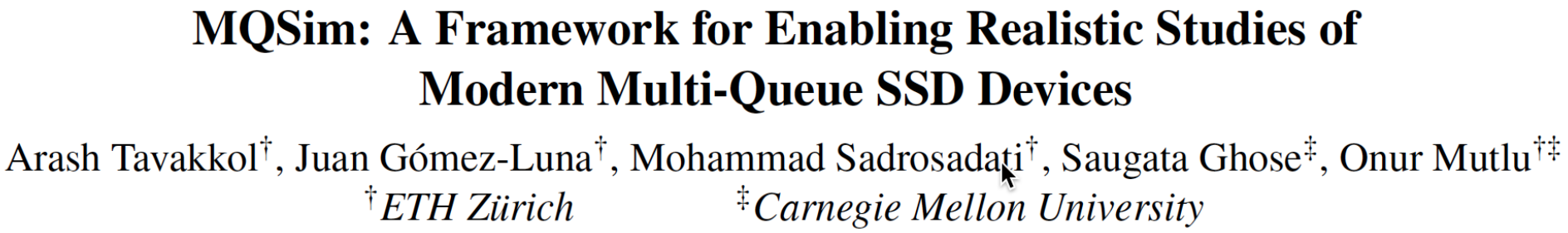
This paper reviews the most recent advances in solid-state drive (SSD) error characterization, mitigation, and data recovery techniques to improve both SSD's reliability and lifetime.

By Yu Cai, Saugata Ghose, Erich F. Haratsch, Yixin Luo, and Onur Mutlu

https://arxiv.org/pdf/1706.08642

On Modern SSD Controllers (II)

- Arash Tavakkol, Juan Gomez-Luna, Mohammad Sadrosadati, Saugata Ghose, and Onur Mutlu,
  "MQSim: A Framework for Enabling Realistic Studies of Modern Multi-Queue SSD Devices"
  *Proceedings of the 16th USENIX Conference on File and Storage Technologies (**FAST**)*, Oakland, CA, USA, February 2018.
  [Slides (pptx) (pdf)]
  [Source Code]


MQSim: A Framework for Enabling Realistic Studies of Modern Multi-Queue SSD Devices

Arash Tavakkol[†], Juan Gómez-Luna[†], Mohammad Sadrosadati[†], Saugata Ghose[‡], Onur Mutlu[†‡]

[†]*ETH Zürich* [‡]*Carnegie Mellon University*

On Modern SSD Controllers (III)

- Arash Tavakkol, Mohammad Sadrosadati, Saugata Ghose, Jeremie Kim, Yixin Luo, Yaohua Wang, Nika Mansouri Ghiasi, Lois Orosa, Juan G. Luna and Onur Mutlu,
  "FLIN: Enabling Fairness and Enhancing Performance in Modern NVMe Solid State Drives"
  *Proceedings of the 45th International Symposium on Computer Architecture (**ISCA**)*, Los Angeles, CA, USA, June 2018.
  [Slides (pptx) (pdf)] [Lightning Talk Slides (pptx) (pdf)]
  [Lightning Talk Video]

FLIN: Enabling Fairness and Enhancing Performance in Modern NVMe Solid State Drives

Arash Tavakkol[†] Mohammad Sadrosadati[†] Saugata Ghose[‡] Jeremie S. Kim[‡†] Yixin Luo[‡]
Yaohua Wang[†§] Nika Mansouri Ghiasi[†] Lois Orosa[†*] Juan Gómez-Luna[†] Onur Mutlu[†‡]
[†]*ETH Zürich* [‡]*Carnegie Mellon University* [§]*NUDT* [*]*Unicamp*

DRAM Types

- DRAM has different types with different interfaces optimized for different purposes
  - Commodity: DDR, DDR2, DDR3, DDR4, …
  - Low power (for mobile): LPDDR1, …, LPDDR5, …
  - High bandwidth (for graphics): GDDR2, …, GDDR5, …
  - Low latency: eDRAM, RLDRAM, …
  - 3D stacked: WIO, HBM, HMC, …
  - …
- Underlying microarchitecture is fundamentally the same
- A flexible memory controller can support various DRAM types
- This complicates the memory controller
  - Difficult to support all types (and upgrades)

DRAM Types (circa 2015)

Segment	*DRAM Standards & Architectures*
Commodity	DDR3 (2007) [14]; DDR4 (2012) [18]
Low-Power	LPDDR3 (2012) [17]; LPDDR4 (2014) [20]
Graphics	GDDR5 (2009) [15]
Performance	eDRAM [28], [32]; RLDRAM3 (2011) [29]
3D-Stacked	WIO (2011) [16]; WIO2 (2014) [21]; MCDRAM (2015) [13]; HBM (2013) [19]; HMC1.0 (2013) [10]; HMC1.1 (2014) [11]
Academic	SBA/SSA (2010) [38]; Staged Reads (2012) [8]; RAIDR (2012) [27]; SALP (2012) [24]; TL-DRAM (2013) [26]; RowClone (2013) [37]; Half-DRAM (2014) [39]; Row-Buffer Decoupling (2014) [33]; SARP (2014) [6]; AL-DRAM (2015) [25]

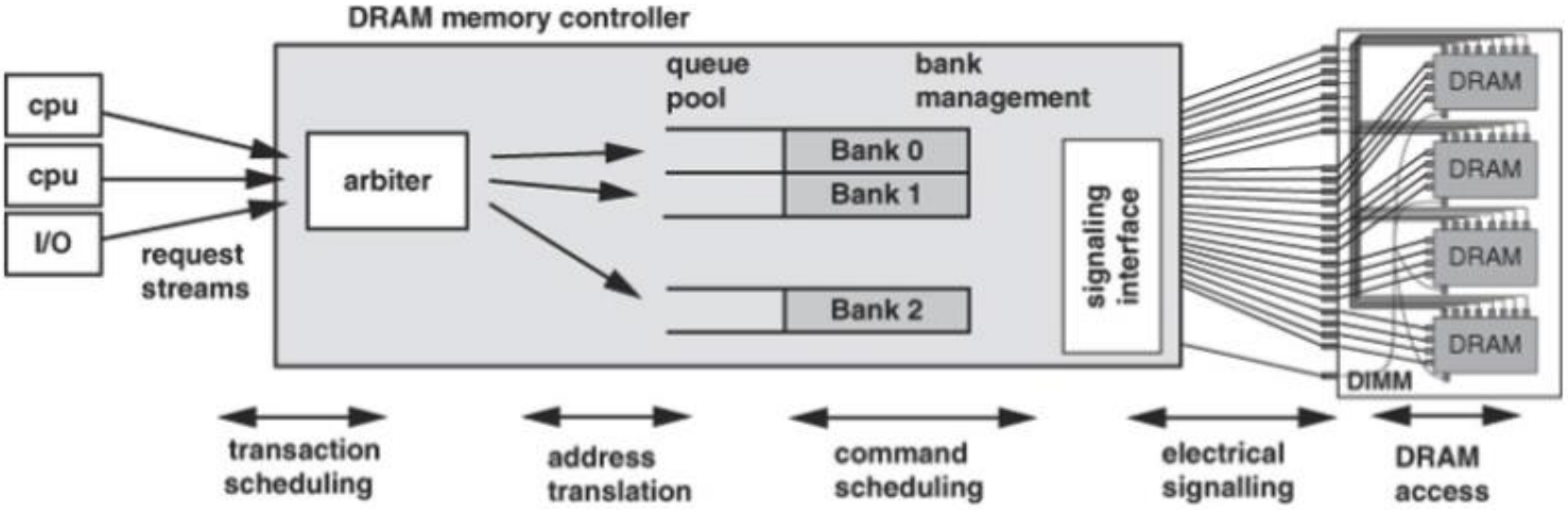
Table 1. Landscape of DRAM-based memory

Kim et al., "Ramulator: A Fast and Extensible DRAM Simulator," IEEE Comp Arch Letters 2015.

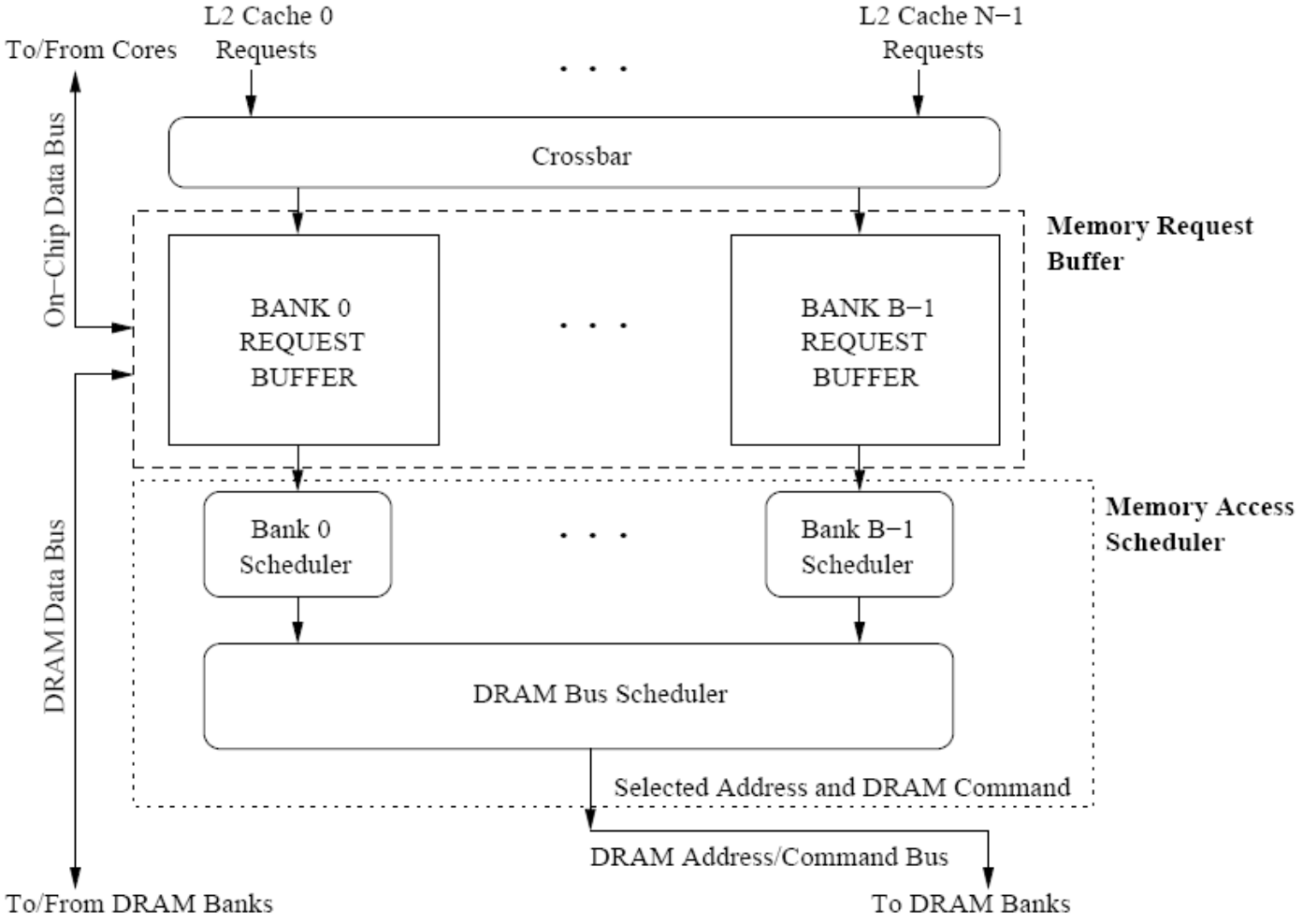
DRAM Controller: Functions

- Ensure correct operation of DRAM (refresh and timing)
- Service DRAM requests while obeying timing constraints of DRAM chips
  - Constraints: resource conflicts (bank, bus, channel), minimum write-to-read delays
  - Translate requests to DRAM command sequences
- Buffer and schedule requests to for high performance + QoS
  - Reordering, row-buffer, bank, rank, bus management
- Manage power consumption and thermals in DRAM
  - Turn on/off DRAM chips, manage power modes

A Modern DRAM Controller (I)



A Modern DRAM Controller



DRAM Scheduling Policies (I)

- FCFS (first come first served)
  - Oldest request first

- FR-FCFS (first ready, first come first served)

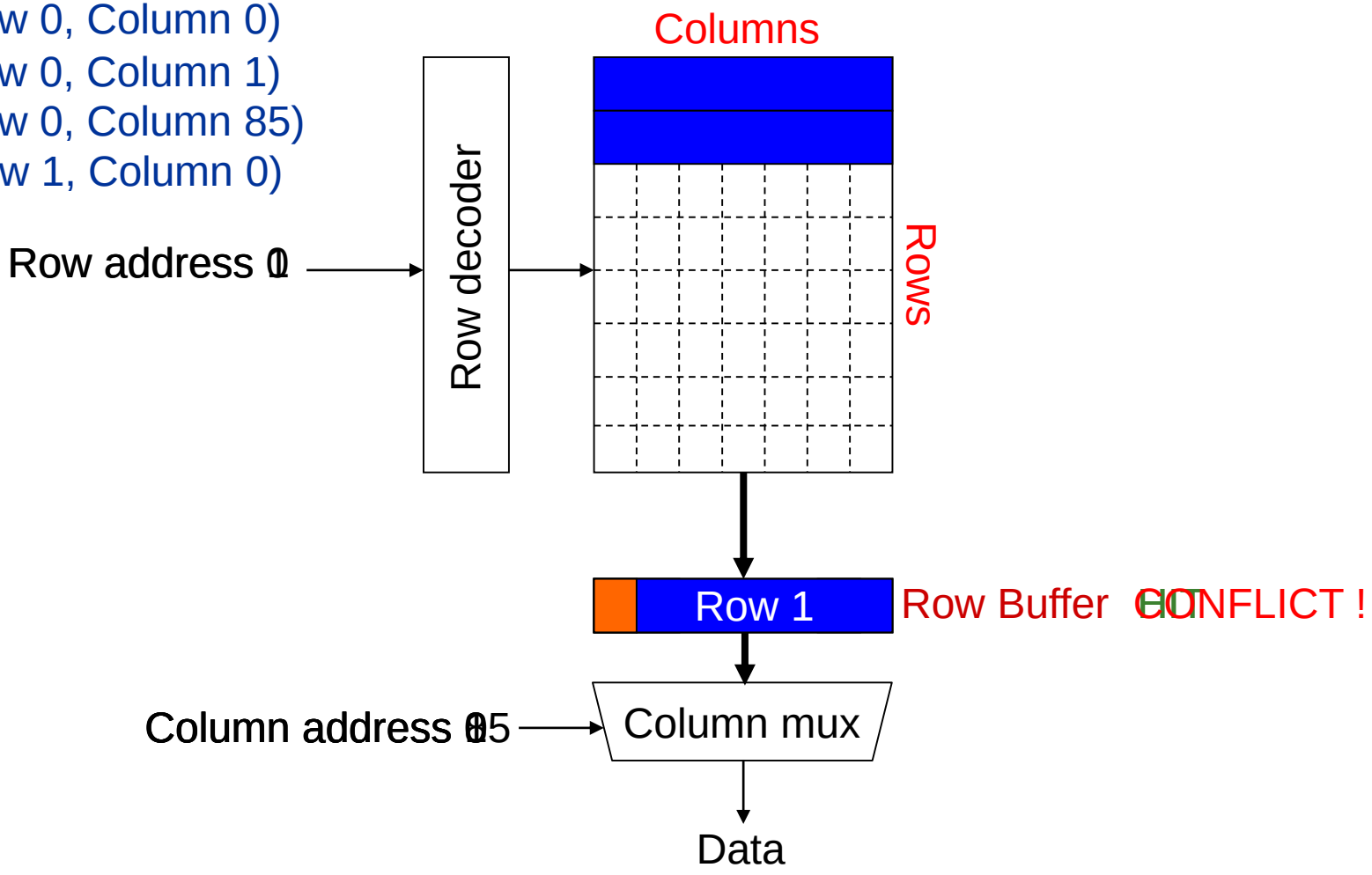
  1. Row-hit first
  2. Oldest first

  Goal: Maximize row buffer hit rate → maximize DRAM throughput

  - Actually, scheduling is done at the command level
    - Column commands (read/write) prioritized over row commands (activate/precharge)
    - Within each group, older commands prioritized over younger ones

Review: DRAM Bank Operation

Access Address:
(Row 0, Column 0)
(Row 0, Column 1)
(Row 0, Column 85)
(Row 1, Column 0)



DRAM Scheduling Policies (II)

- A scheduling policy is a request prioritization order

- Prioritization can be based on
  - Request age
  - Row buffer hit/miss status
  - Request type (prefetch, read, write)
  - Requestor type (load miss or store miss)
  - Request criticality
    - Oldest miss in the core?
    - How many instructions in core are dependent on it?
    - Will it stall the processor?
  - Interference caused to other cores
  - ...

Row Buffer Management Policies

- Open row
  - Keep the row open after an access

  + Next access might need the same row → row hit

  -- Next access might need a different row → row conflict, wasted energy

- Closed row
  - Close the row after an access (if no other requests already in the request buffer need the same row)

  + Next access might need a different row → avoid a row conflict

  -- Next access might need the same row → extra activate latency

- Adaptive policies
  - Predict whether or not the next access to the bank will be to the same row and act accordingly

Open vs. Closed Row Policies

Policy	First access	Next access	Commands needed for next access
Open row	Row 0	Row 0 (row hit)	Read
Open row	Row 0	Row 1 (row conflict)	Precharge + Activate Row 1 + Read
Closed row	Row 0	Row 0 – access in request buffer (row hit)	Read
Closed row	Row 0	Row 0 – access not in request buffer (row closed)	Activate Row 0 + Read + Precharge
Closed row	Row 0	Row 1 (row closed)	Activate Row 1 + Read + Precharge

DRAM Power Management

- DRAM chips have power modes
- Idea: When not accessing a chip power it down

- Power states
  - Active (highest power)
  - All banks idle
  - Power-down
  - Self-refresh (lowest power)

- Tradeoff: State transitions incur latency during which the chip cannot be accessed

Difficulty of DRAM Control

Why are DRAM Controllers Difficult to Design?

- Need to obey DRAM timing constraints for correctness
  - There are many (50+) timing constraints in DRAM
  - tWTR: Minimum number of cycles to wait before issuing a read command after a write command is issued
  - tRC: Minimum number of cycles between the issuing of two consecutive activate commands to the same bank
  - …
- Need to keep track of many resources to prevent conflicts
  - Channels, banks, ranks, data bus, address bus, row buffers
- Need to handle DRAM refresh
- Need to manage power consumption
- Need to optimize performance & QoS (in the presence of constraints)
  - Reordering is not simple
  - Fairness and QoS needs complicates the scheduling problem

Many DRAM Timing Constraints

Latency	Symbol	DRAM cycles	Latency	Symbol	DRAM cycles
Precharge	^tRP	11	Activate to read/write	^tRCD	11
Read column address strobe	CL	11	Write column address strobe	CWL	8
Additive	AL	0	Activate to activate	^tRC	39
Activate to precharge	^tRAS	28	Read to precharge	^tRTP	6
Burst length	^tBL	4	Column address strobe to column address strobe	^tCCD	4
Activate to activate (different bank)	^tRRD	6	Four activate windows	^tFAW	24
Write to read	^tWTR	6	Write recovery	^tWR	12

Table 4. DDR3 1600 DRAM timing specifications

- From Lee et al., "DRAM-Aware Last-Level Cache Writeback: Reducing Write-Caused Interference in Memory Systems," HPS Technical Report, April 2010.

More on DRAM Operation

- Kim et al., "A Case for Exploiting Subarray-Level Parallelism (SALP) in DRAM," ISCA 2012.
- Lee et al., "Tiered-Latency DRAM: A Low Latency and Low Cost DRAM Architecture," HPCA 2013.

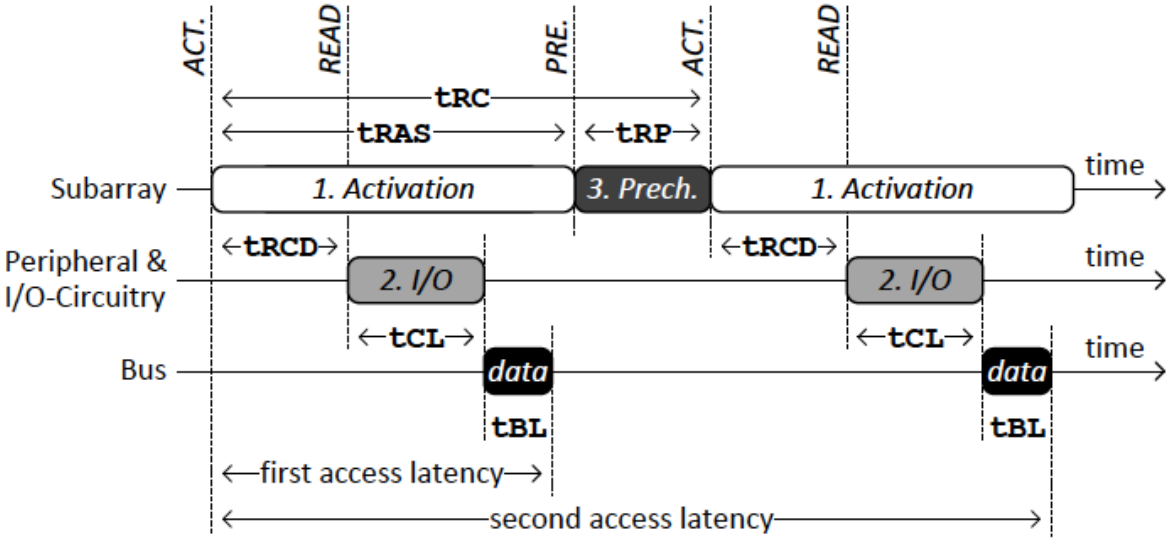


Figure 5. Three Phases of DRAM Access

Table 2. Timing Constraints (DDR3-1066) [43]

Phase	Commands	Name	Value
1	ACT → READ ACT → WRITE	tRCD	15ns
	ACT → PRE	tRAS	37.5ns
2	READ → *data* WRITE → *data*	tCL tCWL	15ns 11.25ns
	data burst	tBL	7.5ns
3	PRE → ACT	tRP	15ns
1 & 3	ACT → ACT	tRC (tRAS+tRP)	52.5ns

Why So Many Timing Constraints? (I)

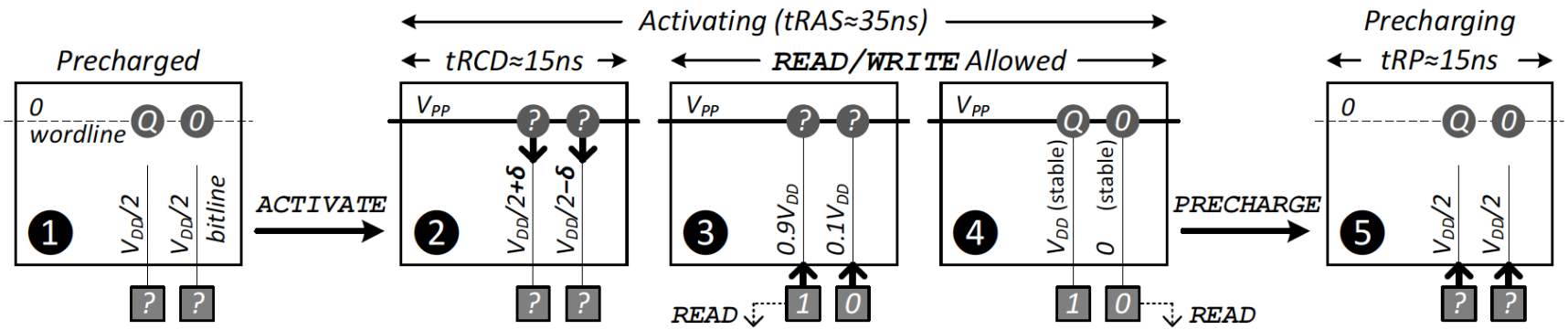


Figure 4. DRAM bank operation: Steps involved in serving a memory request [17] ($V_{PP} > V_{DD}$)

Category	RowCmd↔RowCmd			RowCmd↔ColCmd			ColCmd↔ColCmd			ColCmd→DATA	
Name	*tRC*	*tRAS*	*tRP*	*tRCD*	*tRTP*	*tWR**	*tCCD*	*tRTW*†	*tWTR**	*CL*	*CWL*
Commands	A→A	A→P	P→A	A→R/W	R→P	W*→P	R(W)→R(W)	R→W	W*→R	R→DATA	W→DATA
Scope	Bank	Bank	Bank	Bank	Bank	Bank	Channel	Rank	Rank	Bank	Bank
Value (ns)	**~50**	~35	13-15	13-15	~7.5	**15**	5-7.5	11-15	~7.5	13-15	10-15

A: ACTIVATE– P: PRECHARGE– R: READ– W: WRITE

∗ Goes into effect after the last write *data*, not from the WRITE command

† Not explicitly specified by the JEDEC DDR3 standard [18]. Defined as a function of other timing constraints.

Table 1. Summary of DDR3-SDRAM timing constraints (derived from Micron's 2Gb DDR3-SDRAM datasheet [33])

Kim et al., "A Case for Exploiting Subarray-Level Parallelism (SALP) in DRAM," ISCA 2012.

Why So Many Timing Constraints? (II)

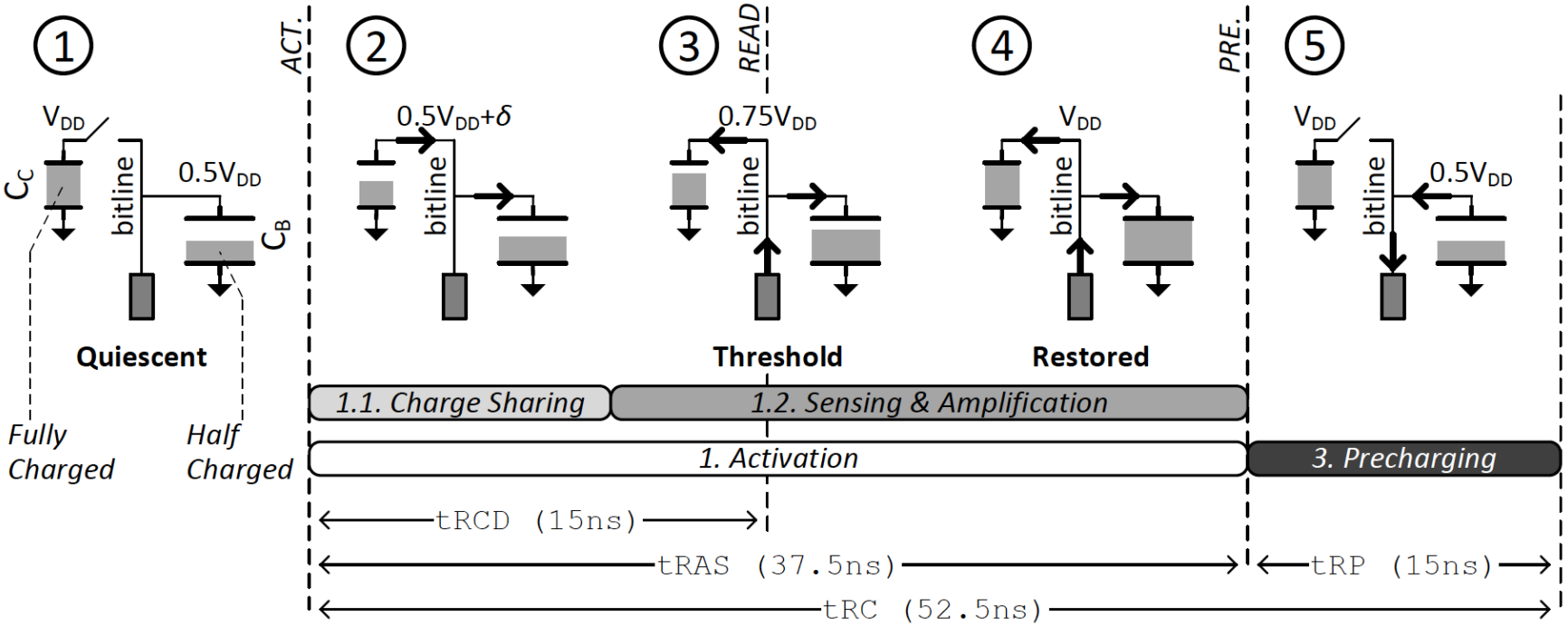


Figure 6. Charge Flow Between the Cell Capacitor (C_C), Bitline Parasitic Capacitor (C_B), and the Sense-Amplifier ($C_B \approx 3.5C_C$ [39])

Lee et al., "Tiered-Latency DRAM: A Low Latency and Low Cost DRAM Architecture," HPCA 2013.

Table 2. Timing Constraints (DDR3-1066) [43]

Phase	Commands	Name	Value
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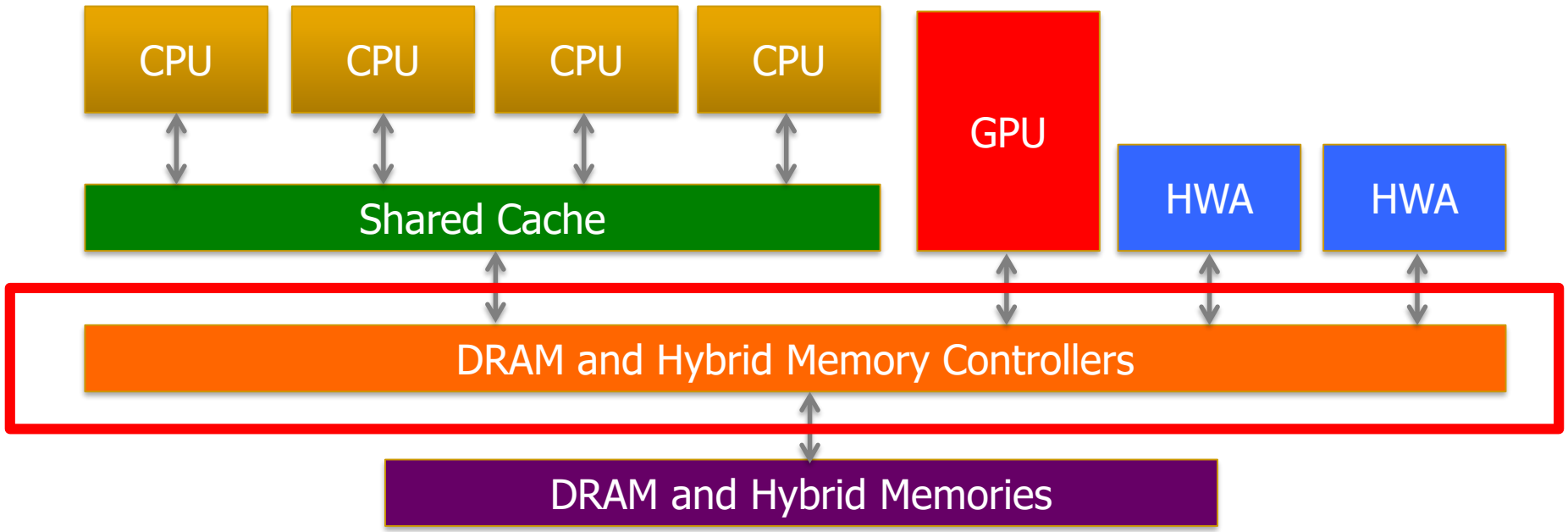
2	READ → *data* WRITE → *data*	tCL tCWL	15ns 11.25ns
	data burst	tBL	7.5ns
3	PRE → ACT	tRP	15ns
1 & 3	ACT → ACT	tRC (tRAS+tRP)	52.5ns

DRAM Controller Design Is Becoming More Difficult



- Heterogeneous agents: CPUs, GPUs, and HWAs
- Main memory interference between CPUs, GPUs, HWAs
- Many timing constraints for various memory types
- Many goals at the same time: performance, fairness, QoS, energy efficiency, …

Reality and Dream

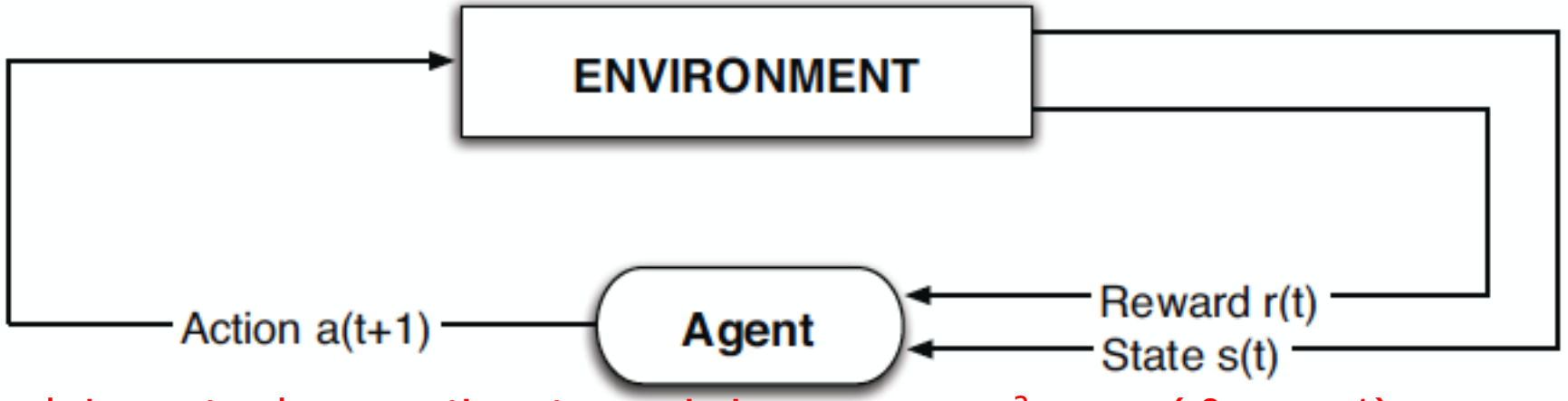
- Reality: It difficult to optimize all these different constraints while maximizing performance, QoS, energy-efficiency, …
- Dream: Wouldn't it be nice if the DRAM controller automatically found a good scheduling policy on its own?

Self-Optimizing DRAM Controllers

- Problem: DRAM controllers difficult to design → It is difficult for human designers to design a policy that can adapt itself very well to different workloads and different system conditions
- Idea: Design a memory controller that adapts its scheduling policy decisions to workload behavior and system conditions using machine learning.
- Observation: Reinforcement learning maps nicely to memory control.
- Design: Memory controller is a reinforcement learning agent that dynamically and continuously learns and employs the best scheduling policy.

Ipek+, "Self Optimizing Memory Controllers: A Reinforcement Learning Approach," ISCA 2008.

Self-Optimizing DRAM Controllers

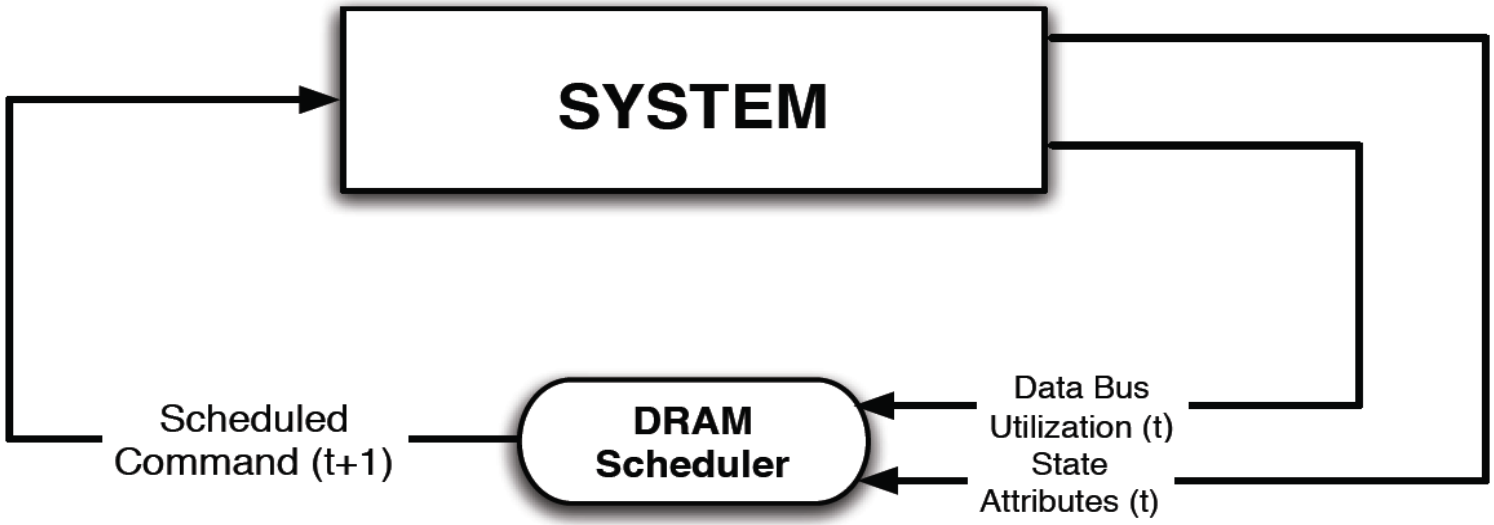


Goal: Learn to choose actions to maximize $r_0 + \gamma r_1 + \gamma^2 r_2 + \ldots$ ($0 \leq \gamma < 1$)

Figure 2: (a) Intelligent agent based on reinforcement learning principles;

Self-Optimizing DRAM Controllers

- Dynamically adapt the memory scheduling policy via interaction with the system at runtime
  - Associate system states and actions (commands) with long term reward values: each action at a given state leads to a learned reward
  - Schedule command with highest estimated long-term reward value in each state
  - Continuously update reward values for <state, action> pairs based on feedback from system



Self-Optimizing DRAM Controllers

- Engin Ipek, Onur Mutlu, José F. Martínez, and Rich Caruana, **"Self Optimizing Memory Controllers: A Reinforcement Learning Approach"**
  *Proceedings of the 35th International Symposium on Computer Architecture (**ISCA**)*, pages 39-50, Beijing, China, June 2008.

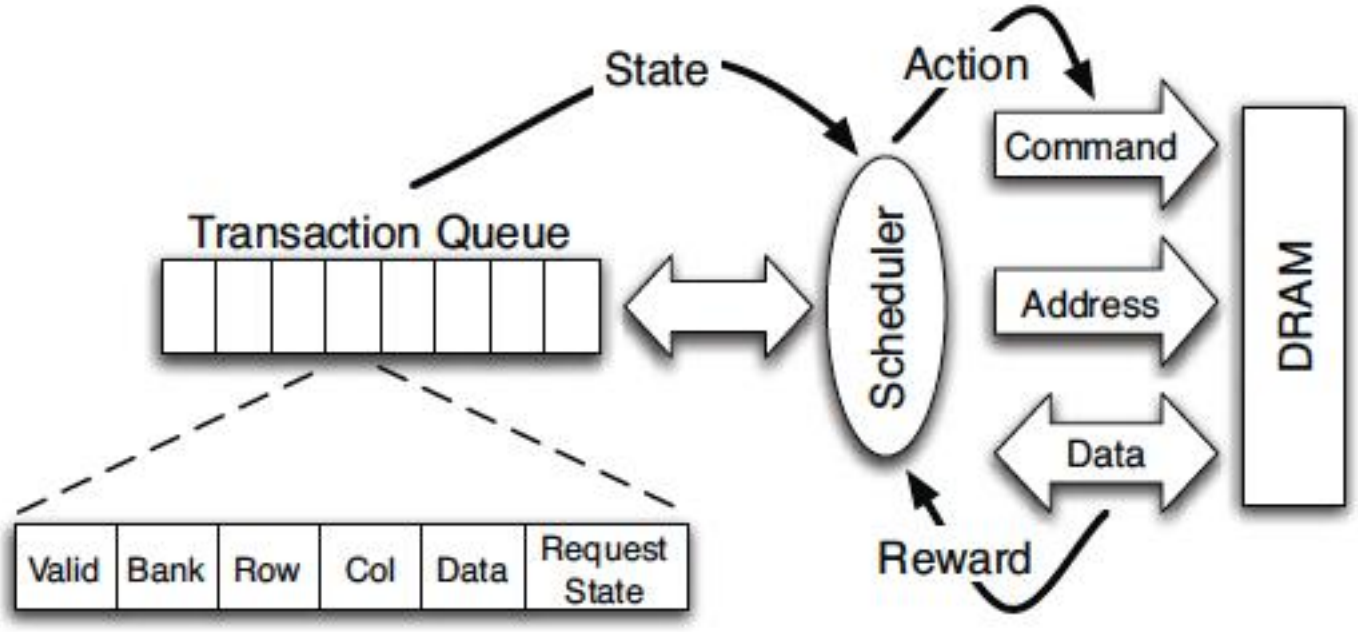


Figure 4: High-level overview of an RL-based scheduler.

States, Actions, Rewards

- Reward function
  - +1 for scheduling Read and Write commands
  - 0 at all other times

  Goal is to maximize long-term data bus utilization
- State attributes
  - Number of reads, writes, and load misses in transaction queue
  - Number of pending writes and ROB heads waiting for referenced row
  - Request's relative ROB order
- Actions
  - Activate
  - Write
  - Read - load miss
  - Read - store miss
  - Precharge - pending
  - Precharge - preemptive
  - NOP

Performance Results

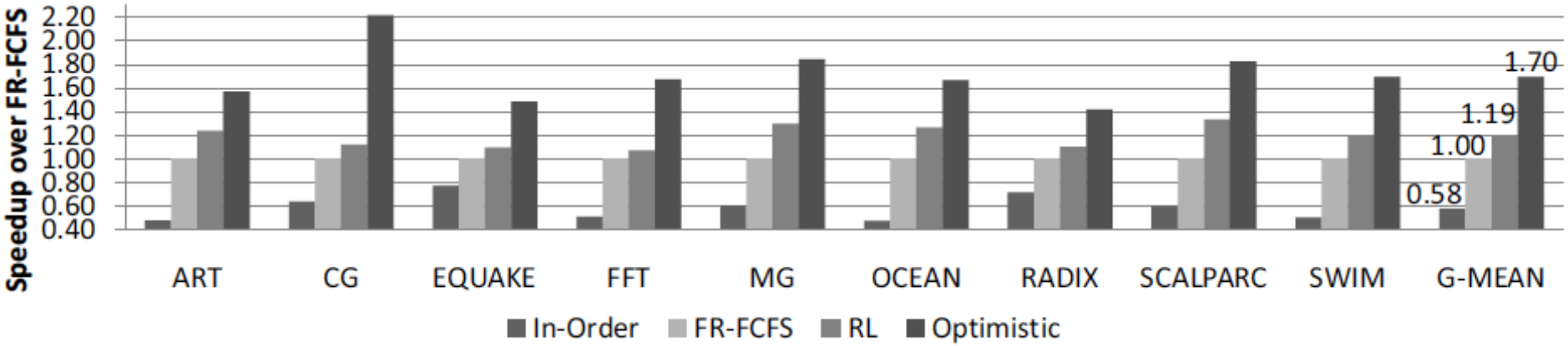


Figure 7: Performance comparison of in-order, FR-FCFS, RL-based, and optimistic memory controllers

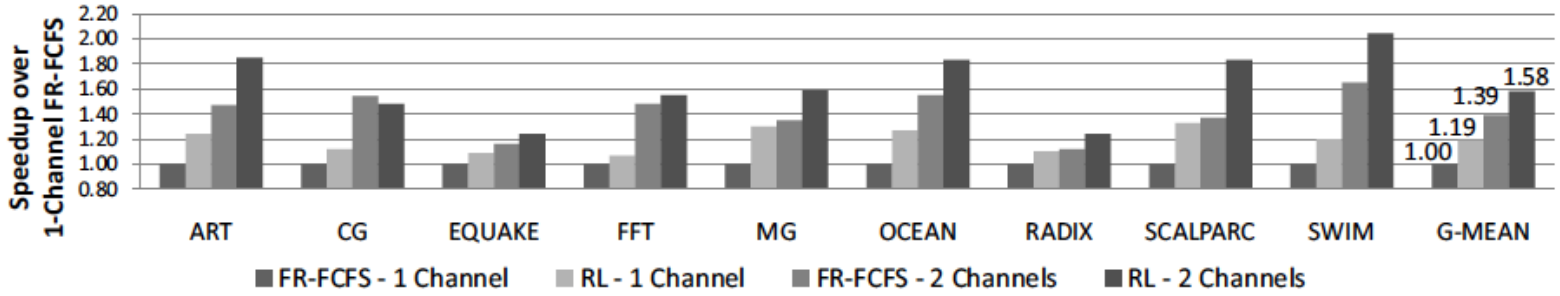


Figure 15: Performance comparison of FR-FCFS and RL-based memory controllers on systems with 6.4GB/s and 12.8GB/s peak DRAM bandwidth

Self Optimizing DRAM Controllers

- Advantages

  + Adapts the scheduling policy dynamically to changing workload behavior and to maximize a long-term target

  + Reduces the designer's burden in finding a good scheduling policy. Designer specifies:

    1) What system variables might be useful

    2) What target to optimize, but not how to optimize it

- Disadvantages and Limitations

  -- Black box: designer much less likely to implement what she cannot easily reason about

  -- How to specify different reward functions that can achieve different objectives? (e.g., fairness, QoS)

  -- Hardware complexity?

More on Self-Optimizing DRAM Controllers

- Engin Ipek, Onur Mutlu, José F. Martínez, and Rich Caruana, **"Self Optimizing Memory Controllers: A Reinforcement Learning Approach"** *Proceedings of the 35th International Symposium on Computer Architecture (**ISCA**)*, pages 39-50, Beijing, China, June 2008.

Self-Optimizing Memory Controllers: A Reinforcement Learning Approach

Engin İpek[1,2] **Onur Mutlu**[2] **José F. Martínez**[1] **Rich Caruana**[1]

[1]Cornell University, Ithaca, NY 14850 USA

[2] Microsoft Research, Redmond, WA 98052 USA

Simulating Memory

Ramulator: A Fast and Extensible DRAM Simulator

[IEEE Comp Arch Letters'15]

Ramulator Motivation

- DRAM and Memory Controller landscape is changing
- Many new and upcoming standards
- Many new controller designs
- A fast and easy-to-extend simulator is very much needed

Segment	*DRAM Standards & Architectures*
Commodity	DDR3 (2007) [14]; DDR4 (2012) [18]
Low-Power	LPDDR3 (2012) [17]; LPDDR4 (2014) [20]
Graphics	GDDR5 (2009) [15]
Performance	eDRAM [28], [32]; RLDRAM3 (2011) [29]
3D-Stacked	WIO (2011) [16]; WIO2 (2014) [21]; MCDRAM (2015) [13]; HBM (2013) [19]; HMC1.0 (2013) [10]; HMC1.1 (2014) [11]
Academic	SBA/SSA (2010) [38]; Staged Reads (2012) [8]; RAIDR (2012) [27]; SALP (2012) [24]; TL-DRAM (2013) [26]; RowClone (2013) [37]; Half-DRAM (2014) [39]; Row-Buffer Decoupling (2014) [33]; SARP (2014) [6]; AL-DRAM (2015) [25]

Table 1. Landscape of DRAM-based memory

Ramulator

- Provides out-of-the box support for many DRAM standards:
  - DDR3/4, LPDDR3/4, GDDR5, WIO1/2, HBM, plus new proposals (SALP, AL-DRAM, TLDRAM, RowClone, and SARP)
- ~2.5X faster than fastest open-source simulator
- Modular and extensible to different standards

Simulator (clang -O3)	*Cycles (10^6)*		*Runtime (sec.)*		*Req/sec (10^3)*		*Memory (MB)*
	Random	*Stream*	*Random*	*Stream*	*Random*	*Stream*	
Ramulator	652	411	752	249	133	402	2.1
DRAMSim2	645	413	2,030	876	49	114	1.2
USIMM	661	409	1,880	750	53	133	4.5
DrSim	647	406	18,109	12,984	6	8	1.6
NVMain	666	413	6,881	5,023	15	20	4,230.0

Table 3. Comparison of five simulators using two traces

Case Study: Comparison of DRAM Standards

Standard	*Rate (MT/s)*	*Timing (CL-RCD-RP)*	*Data-Bus (Width×Chan.)*	*Rank-per-Chan*	*BW (GB/s)*
DDR3	1,600	11-11-11	64-bit × 1	1	11.9
DDR4	2,400	16-16-16	64-bit × 1	1	17.9
SALP†	1,600	11-11-11	64-bit × 1	1	11.9
LPDDR3	1,600	12-15-15	64-bit × 1	1	11.9
LPDDR4	2,400	22-22-22	32-bit × 2*	1	17.9
GDDR5 [12]	6,000	18-18-18	64-bit × 1	1	44.7
HBM	1,000	7-7-7	128-bit × 8*	1	119.2
WIO	266	7-7-7	128-bit × 4*	1	15.9
WIO2	1,066	9-10-10	128-bit × 8*	1	127.2

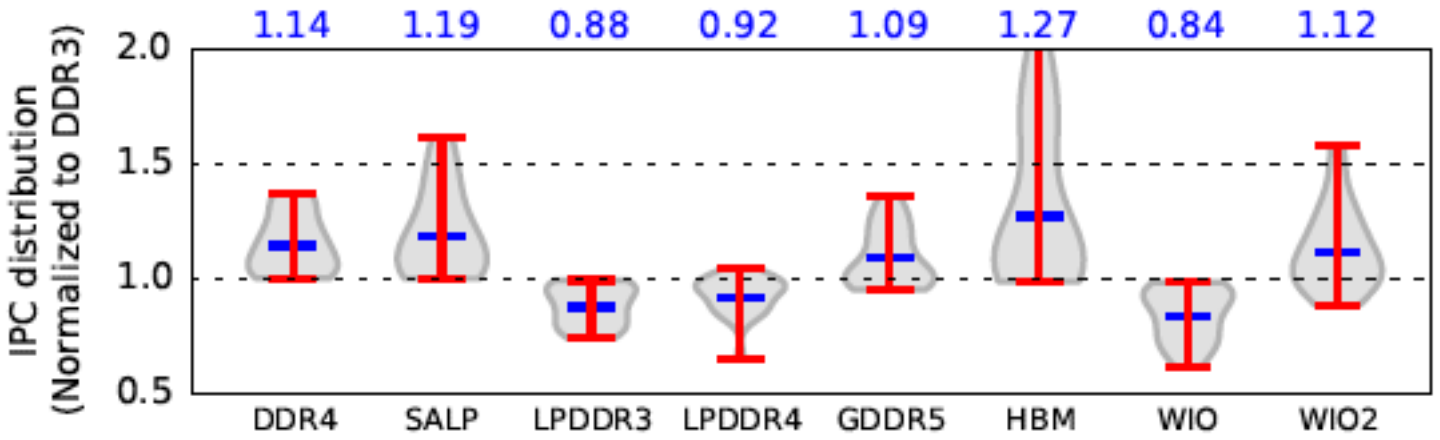


Figure 2. Performance comparison of DRAM standards

Across 22 workloads, simple CPU model

Ramulator Paper and Source Code

- Yoongu Kim, Weikun Yang, and Onur Mutlu,
  "Ramulator: A Fast and Extensible DRAM Simulator"
  IEEE Computer Architecture Letters (***CAL***), March 2015.
  [Source Code]

- Source code is released under the liberal MIT License
  - https://github.com/CMU-SAFARI/ramulator

Ramulator: A Fast and Extensible DRAM Simulator

Yoongu Kim[1] Weikun Yang[1,2] Onur Mutlu[1]
[1]Carnegie Mellon University [2]Peking University

Optional Assignment

- Review the Ramulator paper
  - Email me your review (omutlu@gmail.com)
- Download and run Ramulator
  - Compare DDR3, DDR4, SALP, HBM for the libquantum benchmark (provided in Ramulator repository)
  - Email me your report (omutlu@gmail.com)
- This may help you get into memory systems research quickly

Topics We Will Not Cover

No Time, Unfortunately, for:

- Memory Interference and QoS
- Predictable Performance
  - QoS-aware Memory Controllers
- Emerging Memory Technologies and Hybrid Memories
- Cache Management
- Interconnects
- You can find many materials on these at my online lectures
  - https://people.inf.ethz.ch/omutlu/teaching.html

Some More Suggested Readings

Some Key Readings on DRAM (I)

- DRAM Organization and Operation
  - Lee et al., "Tiered-Latency DRAM: A Low Latency and Low Cost DRAM Architecture," HPCA 2013.
    https://people.inf.ethz.ch/omutlu/pub/tldram_hpca13.pdf
  - Kim et al., "A Case for Subarray-Level Parallelism (SALP) in DRAM," ISCA 2012.
    https://people.inf.ethz.ch/omutlu/pub/salp-dram_isca12.pdf
  - Lee et al., "Simultaneous Multi-Layer Access: Improving 3D-Stacked Memory Bandwidth at Low Cost," ACM TACO 2016.
    https://people.inf.ethz.ch/omutlu/pub/smla_high-bandwidth-3d-stacked-memory_taco16.pdf

Some Key Readings on DRAM (II)

- DRAM Refresh
  - Liu et al., "RAIDR: Retention-Aware Intelligent DRAM Refresh," ISCA 2012.
    https://people.inf.ethz.ch/omutlu/pub/raidr-dram-refresh_isca12.pdf
  - Chang et al., "Improving DRAM Performance by Parallelizing Refreshes with Accesses," HPCA 2014.
    https://people.inf.ethz.ch/omutlu/pub/dram-access-refresh-parallelization_hpca14.pdf
  - Patel et al., "The Reach Profiler (REAPER): Enabling the Mitigation of DRAM Retention Failures via Profiling at Aggressive Conditions," ISCA 2017.
    https://people.inf.ethz.ch/omutlu/pub/reaper-dram-retention-profiling-lpddr4_isca17.pdf

Reading on Simulating Main Memory

- How to evaluate future main memory systems?
- An open-source simulator and its brief description

- Yoongu Kim, Weikun Yang, and Onur Mutlu,
  "Ramulator: A Fast and Extensible DRAM Simulator"
  IEEE Computer Architecture Letters (***CAL***), March 2015.
  [Source Code]

Some Key Readings on Memory Control 1

- Mutlu+, "Parallelism-Aware Batch Scheduling: Enhancing both Performance and Fairness of Shared DRAM Systems," ISCA 2008.
  https://people.inf.ethz.ch/omutlu/pub/parbs_isca08.pdf

- Kim et al., "Thread Cluster Memory Scheduling: Exploiting Differences in Memory Access Behavior," MICRO 2010.
  https://people.inf.ethz.ch/omutlu/pub/tcm_micro10.pdf

- Subramanian et al., "BLISS: Balancing Performance, Fairness and Complexity in Memory Access Scheduling," TPDS 2016.
  https://people.inf.ethz.ch/omutlu/pub/bliss-memory-scheduler_ieee-tpds16.pdf

- Usui et al., "DASH: Deadline-Aware High-Performance Memory Scheduler for Heterogeneous Systems with Hardware Accelerators," TACO 2016.
  https://people.inf.ethz.ch/omutlu/pub/dash_deadline-aware-heterogeneous-memory-scheduler_taco16.pdf

Some Key Readings on Memory Control 2

- Ipek+, "Self Optimizing Memory Controllers: A Reinforcement Learning Approach," ISCA 2008.
  https://people.inf.ethz.ch/omutlu/pub/rlmc_isca08.pdf

- Ebrahimi et al., "Fairness via Source Throttling: A Configurable and High-Performance Fairness Substrate for Multi-Core Memory Systems," ASPLOS 2010.
  https://people.inf.ethz.ch/omutlu/pub/fst_asplos10.pdf

- Subramanian et al., "The Application Slowdown Model: Quantifying and Controlling the Impact of Inter-Application Interference at Shared Caches and Main Memory," MICRO 2015.
  https://people.inf.ethz.ch/omutlu/pub/application-slowdown-model_micro15.pdf

- Lee et al., "Decoupled Direct Memory Access: Isolating CPU and IO Traffic by Leveraging a Dual-Data-Port DRAM," PACT 2015.
  https://people.inf.ethz.ch/omutlu/pub/decoupled-dma_pact15.pdf

More Readings

- To come as we cover the future topics

- Search for "DRAM" or "Memory" in:
  - https://people.inf.ethz.ch/omutlu/projects.htm

Memory Systems and Memory-Centric Computing Systems
Lecture 2, Topic 1: Memory Trends and Basics

Prof. Onur Mutlu
omutlu@gmail.com
https://people.inf.ethz.ch/omutlu

10 July 2018

HiPEAC ACACES Summer School 2018

SAFARI

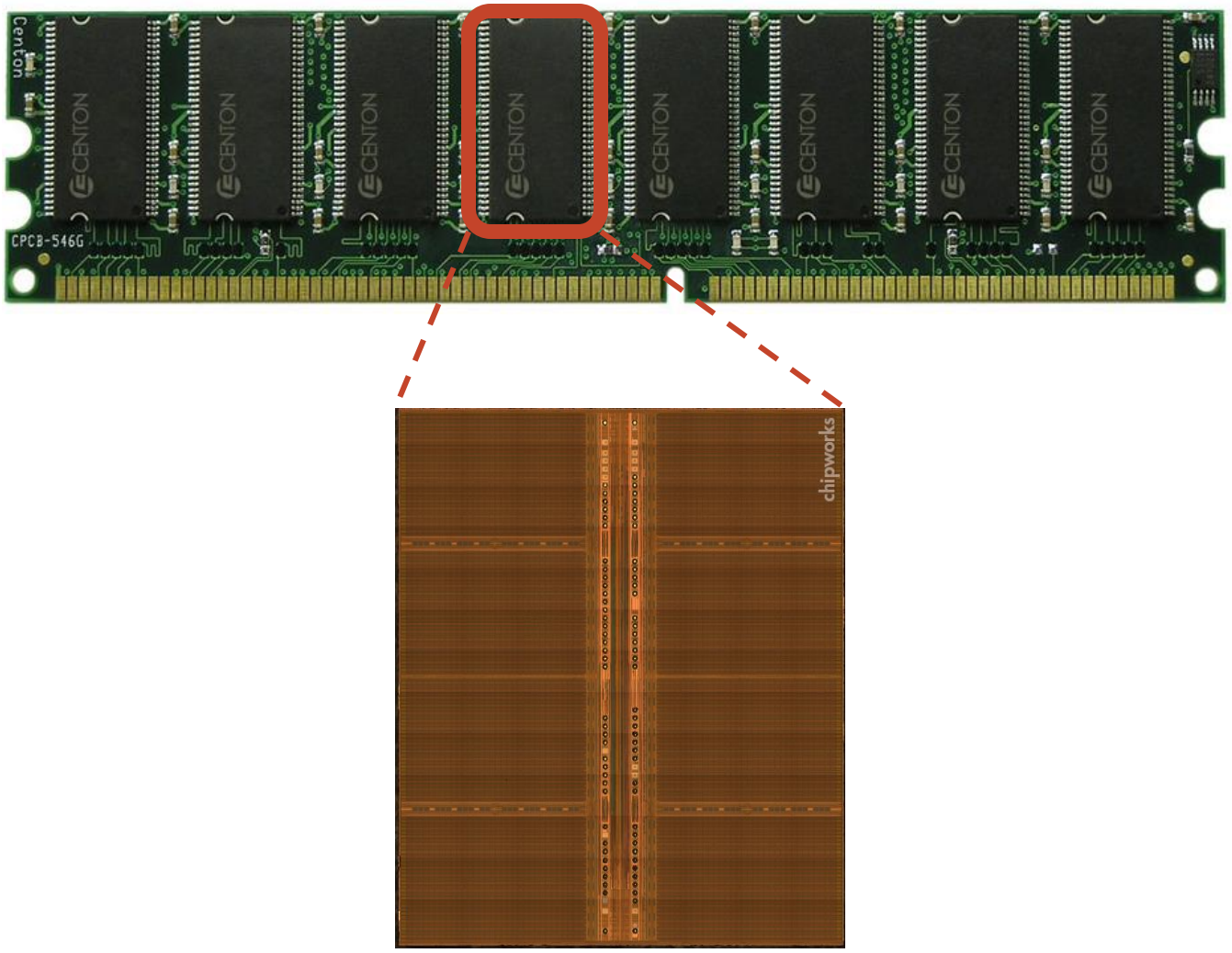
ETH zürich

Carnegie Mellon

Backup Slides

Inside A DRAM Chip

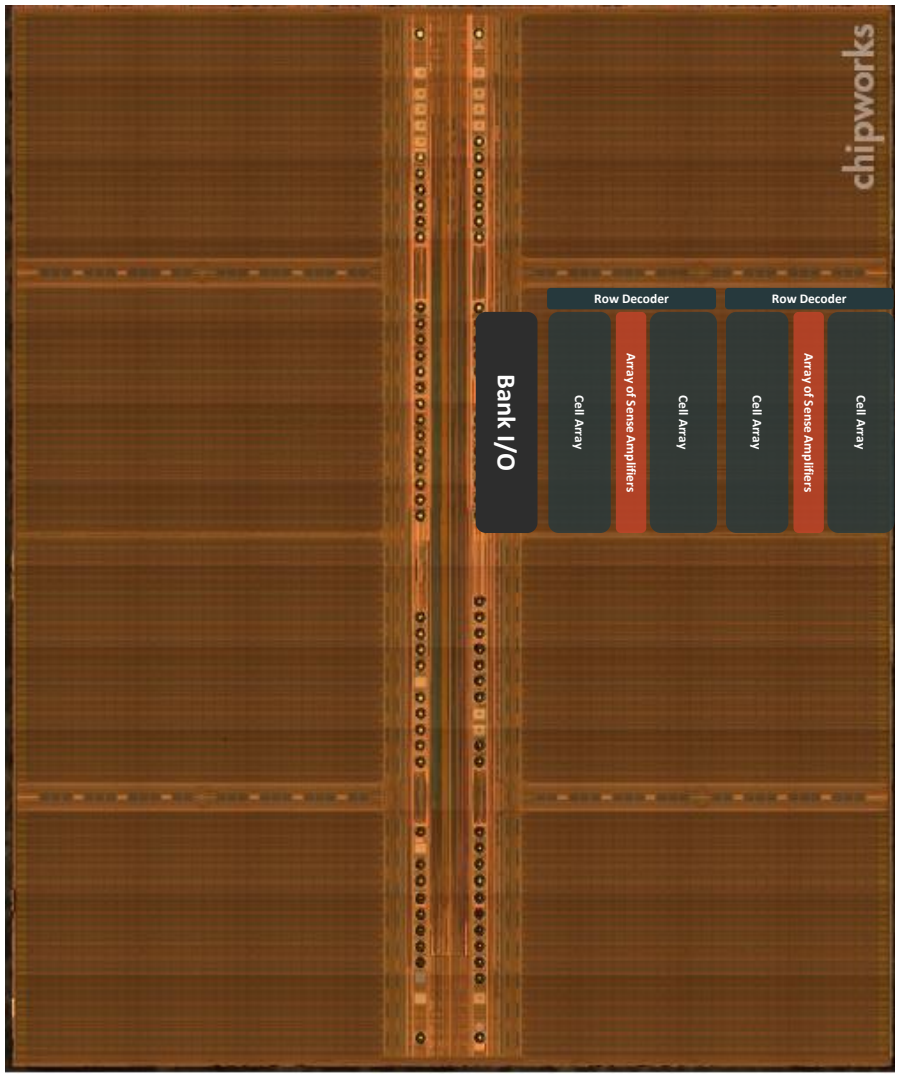
DRAM Module and Chip



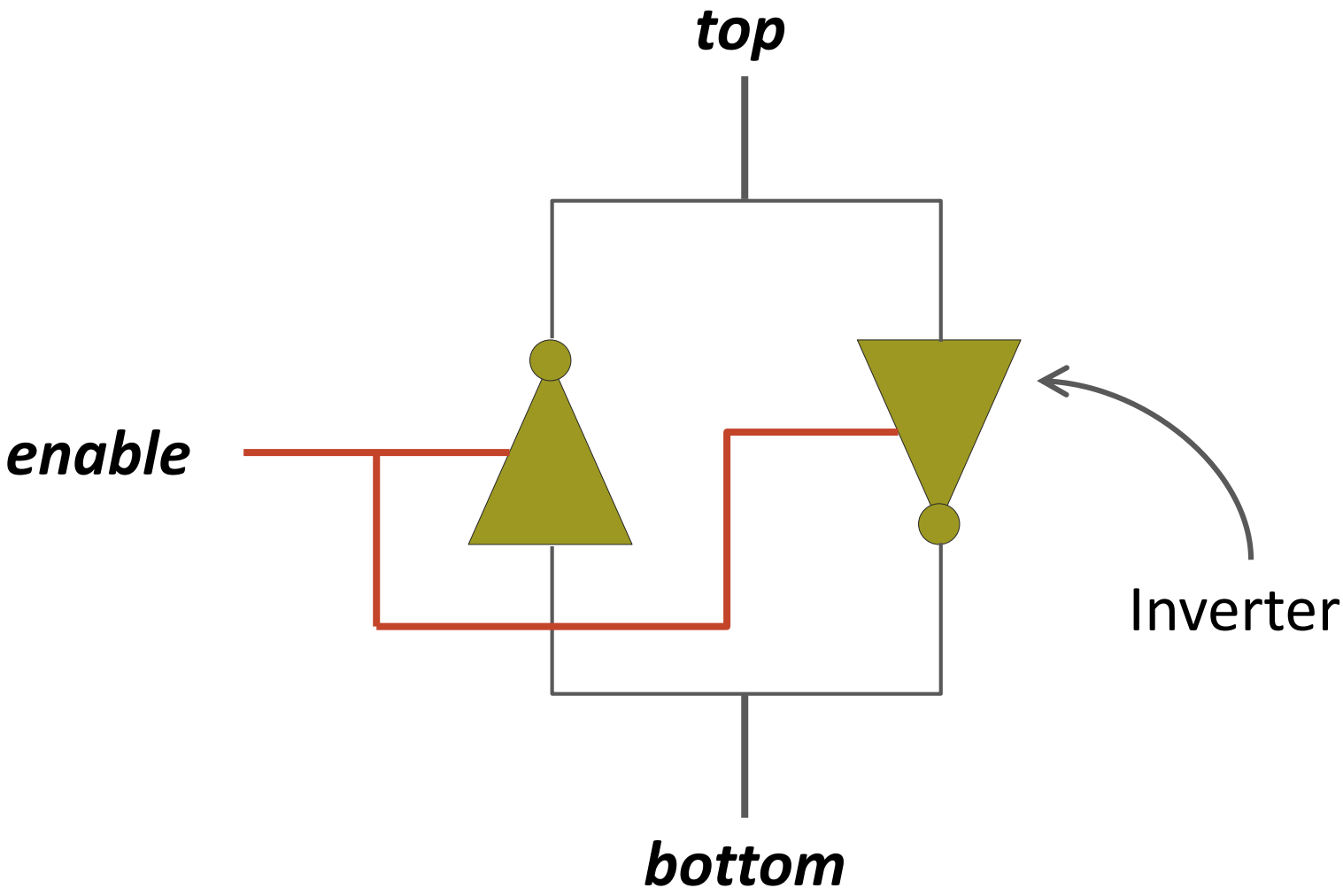
Goals

- Cost
- Latency
- Bandwidth
- Parallelism
- Power
- Energy
- Reliability
- …

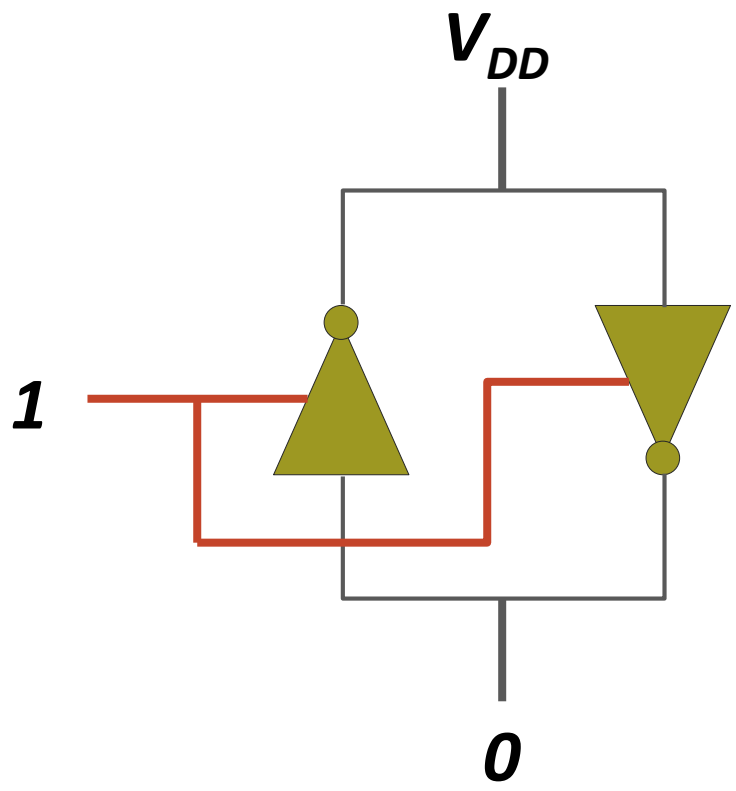
DRAM Chip


chipworks
Row Decoder
Row Decoder
Bank I/O
Cell Array
Array of Sense Amplifiers
Cell Array
Cell Array
Array of Sense Amplifiers
Cell Array

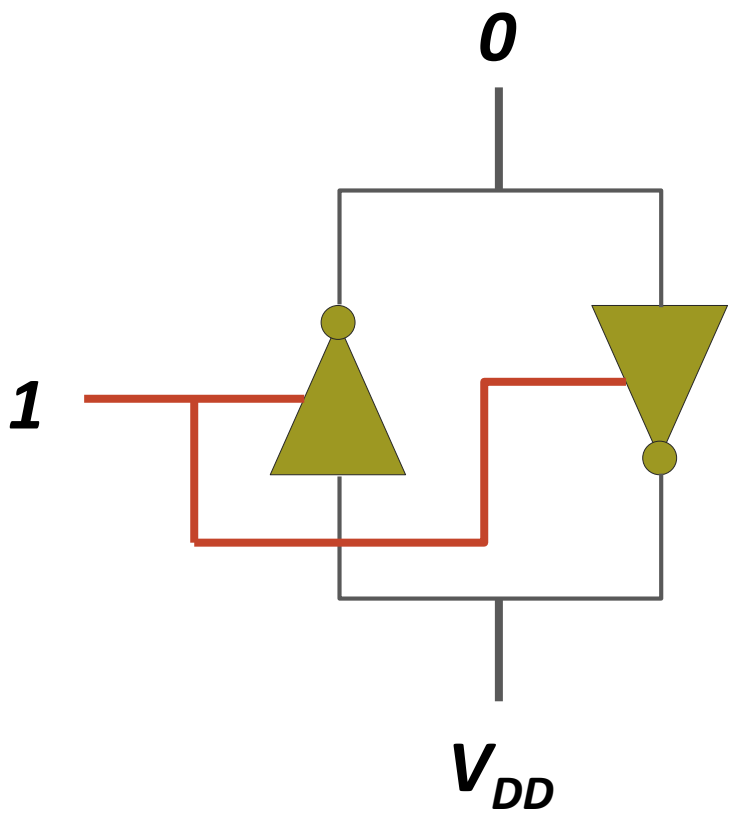
Sense Amplifier



Sense Amplifier – Two Stable States

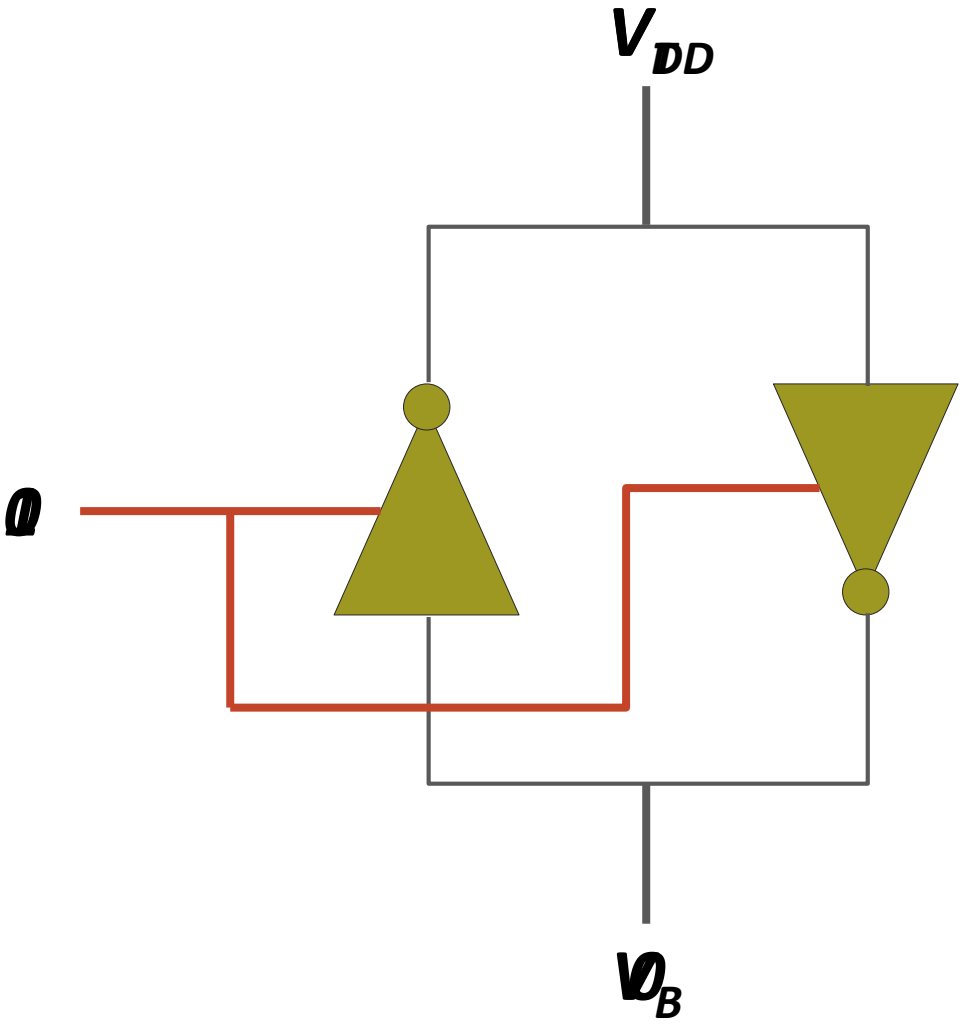


Logical “1”



Logical “0”

Sense Amplifier Operation

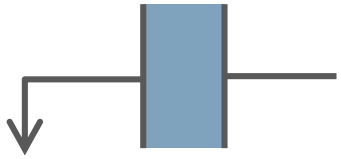


$V_T > V_B$

DRAM Cell – Capacitor

Empty State

Logical “0”

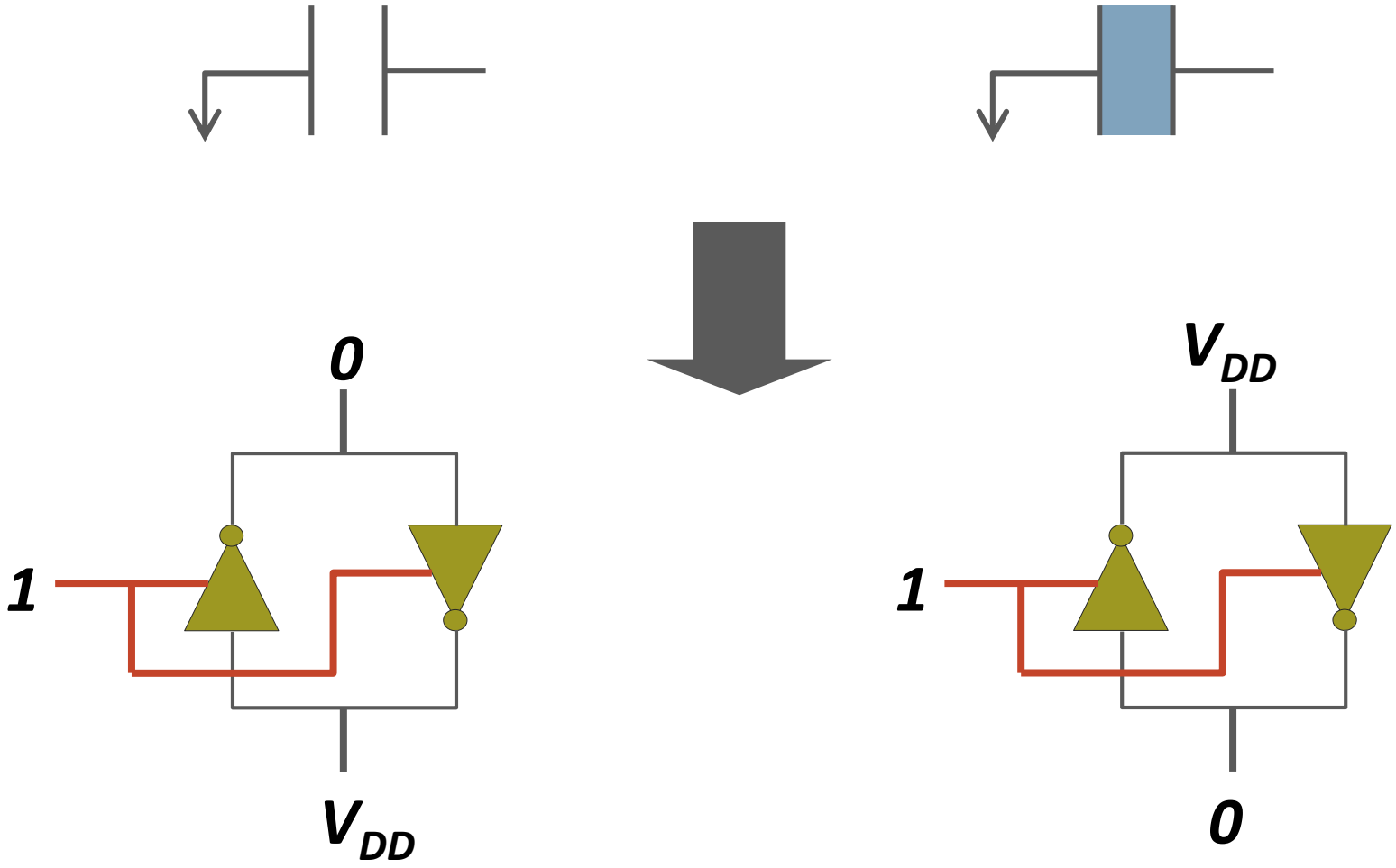


Fully Charged State

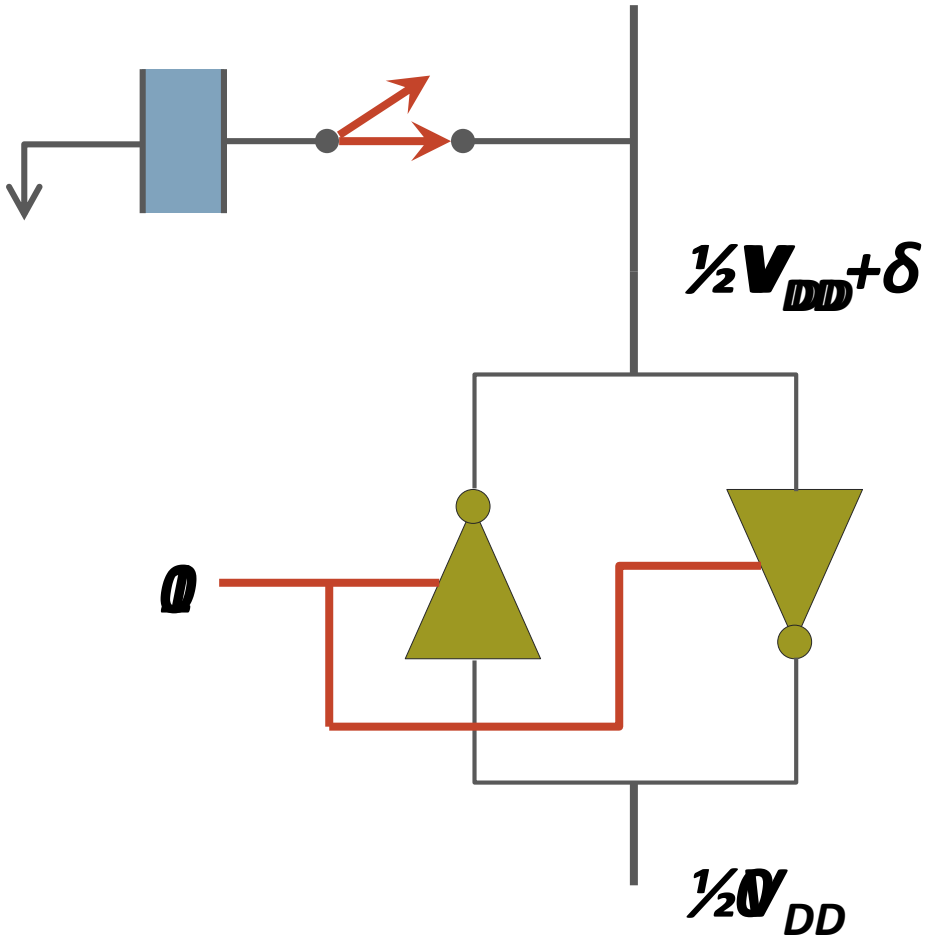
Logical “1”

1. Small – Cannot drive circuits
2. Reading destroys the state

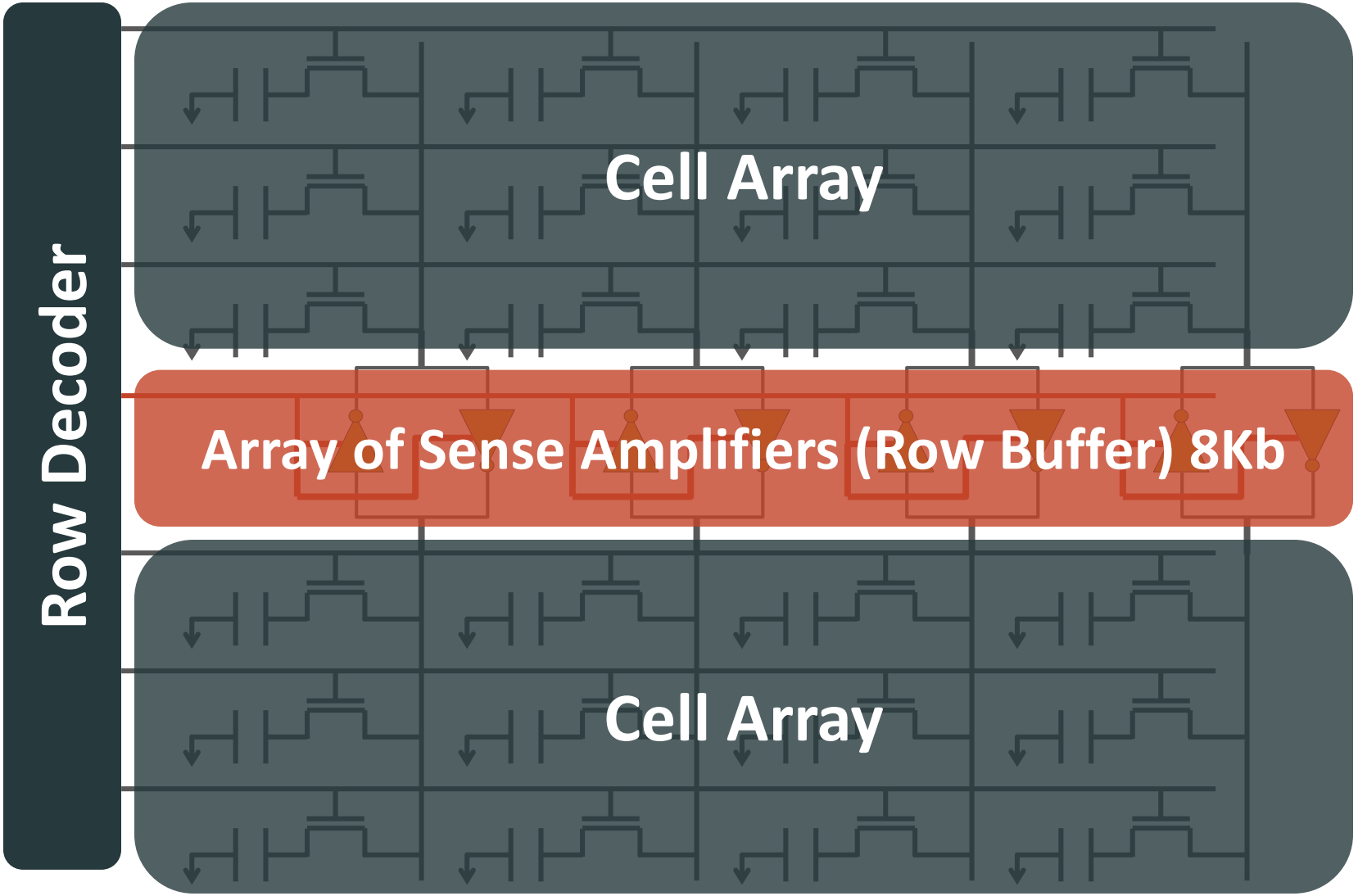
Capacitor to Sense Amplifier



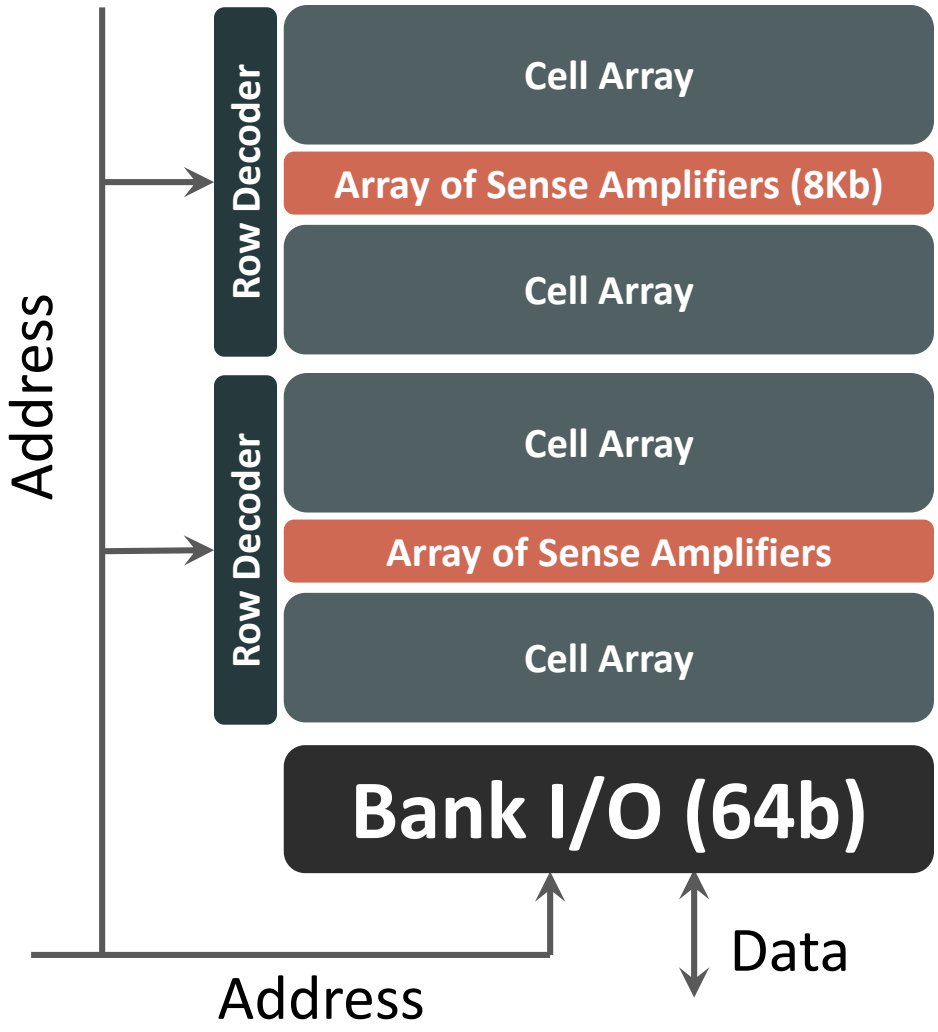
DRAM Cell Operation



DRAM Subarray – Building Block for DRAM Chip

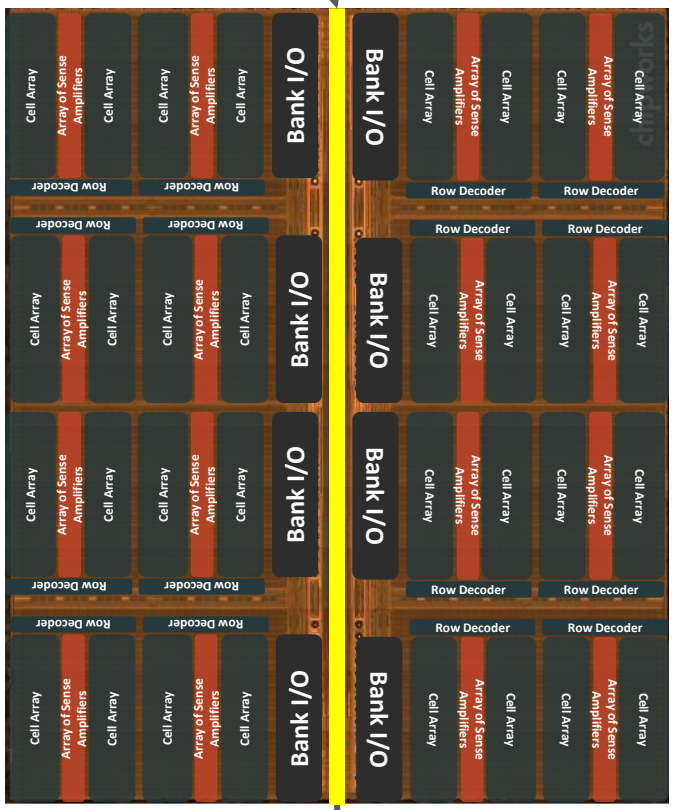


DRAM Bank


Row Decoder
Cell Array
Array of Sense Amplifiers (8Kb)
Cell Array
Row Decoder
Cell Array
Array of Sense Amplifiers
Cell Array
Address
Bank I/O (64b)
Data
Address

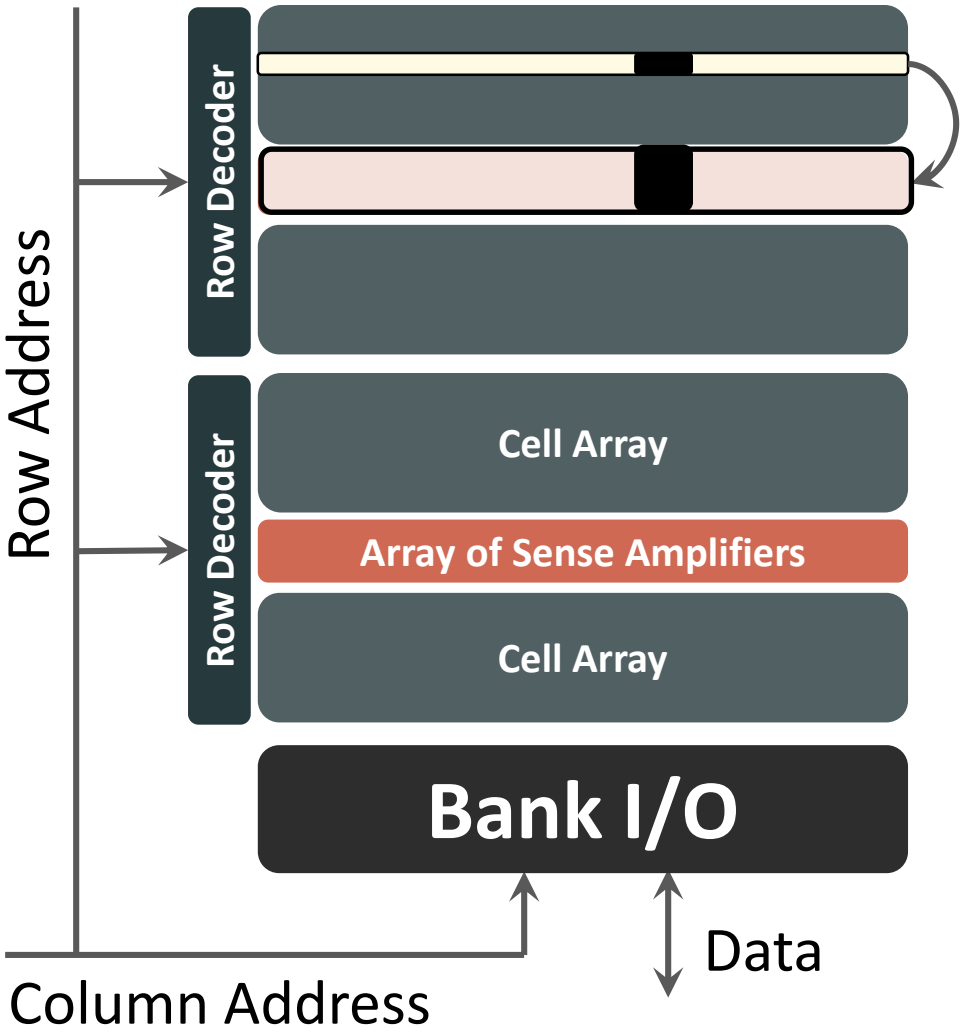
DRAM Chip

Shared internal bus



Memory channel - 8bits

DRAM Operation



1. ACTIVATE Row
2. READ/WRITE Column
3. PRECHARGE

Evaluating New Ideas for New (Memory) Architectures

Potential Evaluation Methods

- How do we assess an idea will improve a target metric X?
- A variety of evaluation methods are available:
  - Theoretical proof
  - Analytical modeling/estimation
  - Simulation (at varying degrees of abstraction and accuracy)
  - Prototyping with a real system (e.g., FPGAs)
  - Real implementation

The Difficulty in Architectural Evaluation

- The answer is usually workload dependent
  - E.g., think caching
  - E.g., think pipelining
  - E.g., think any idea we talked about (RAIDR, Mem. Sched., …)
- Workloads change
- System has many design choices and parameters
  - Architect needs to decide many ideas and many parameters for a design
  - Not easy to evaluate all possible combinations!
- System parameters may change

Simulation: The Field of Dreams

Dreaming and Reality

- An architect is in part a dreamer, a creator
- Simulation is a key tool of the architect
- Simulation enables
  - The exploration of many dreams
  - A reality check of the dreams
  - Deciding which dream is better
- Simulation also enables
  - The ability to fool yourself with false dreams

Why High-Level Simulation?

- Problem: RTL simulation is intractable for design space exploration → too time consuming to design and evaluate
  - Especially over a large number of workloads
  - Especially if you want to predict the performance of a good chunk of a workload on a particular design
  - Especially if you want to consider many design choices
    - Cache size, associativity, block size, algorithms
    - Memory control and scheduling algorithms
    - In-order vs. out-of-order execution
    - Reservation station sizes, ld/st queue size, register file size, …
    - …
- Goal: Explore design choices quickly to see their impact on the workloads we are designing the platform for

Different Goals in Simulation

- Explore the design space quickly and see what you want to
  - potentially implement in a next-generation platform
  - propose as the next big idea to advance the state of the art
  - the goal is mainly to see relative effects of design decisions
- Match the behavior of an existing system so that you can
  - debug and verify it at cycle-level accuracy
  - propose small tweaks to the design that can make a difference in performance or energy
  - the goal is very high accuracy
- Other goals in-between:
  - Refine the explored design space without going into a full detailed, cycle-accurate design
  - Gain confidence in your design decisions made by higher-level design space exploration

Tradeoffs in Simulation

- Three metrics to evaluate a simulator
  - Speed
  - Flexibility
  - Accuracy

- Speed: How fast the simulator runs (xIPS, xCPS, slowdown)
- Flexibility: How quickly one can modify the simulator to evaluate different algorithms and design choices?
- Accuracy: How accurate the performance (energy) numbers the simulator generates are vs. a real design (Simulation error)

- The relative importance of these metrics varies depending on where you are in the design process (what your goal is)

Trading Off Speed, Flexibility, Accuracy

- Speed & flexibility affect:
  - How quickly you can make design tradeoffs
- Accuracy affects:
  - How good your design tradeoffs may end up being
  - How fast you can build your simulator (simulator design time)
- Flexibility also affects:
  - How much human effort you need to spend modifying the simulator
- You can trade off between the three to achieve design exploration and decision goals

High-Level Simulation

- Key Idea: Raise the abstraction level of modeling to give up some accuracy to enable speed & flexibility (and quick simulator design)

- Advantage

  + Can still make the right tradeoffs, and can do it quickly

    + All you need is modeling the key high-level factors, you can omit corner case conditions

    + All you need is to get the "relative trends" accurately, not exact performance numbers

- Disadvantage

  -- Opens up the possibility of potentially wrong decisions

    -- How do you ensure you get the "relative trends" accurately?

Simulation as Progressive Refinement

- High-level models (Abstract, C)
- …
- Medium-level models (Less abstract)
- …
- Low-level models (RTL with everything modeled)
- …
- Real design

- As you refine (go down the above list)
  - Abstraction level reduces
  - Accuracy (hopefully) increases (not necessarily, if not careful)
  - Flexibility reduces; Speed likely reduces except for real design
  - You can loop back and fix higher-level models

Making The Best of Architecture

- A good architect is comfortable at all levels of refinement
  - Including the extremes
- A good architect knows when to use what type of simulation
  - And, more generally, what type of evaluation method
- Recall: A variety of evaluation methods are available:
  - Theoretical proof
  - Analytical modeling
  - Simulation (at varying degrees of abstraction and accuracy)
  - Prototyping with a real system (e.g., FPGAs)
  - Real implementation

Ramulator: A Fast and Extensible DRAM Simulator

[IEEE Comp Arch Letters'15]

Ramulator Motivation

- DRAM and Memory Controller landscape is changing
- Many new and upcoming standards
- Many new controller designs
- A fast and easy-to-extend simulator is very much needed

Segment	*DRAM Standards & Architectures*
Commodity	DDR3 (2007) [14]; DDR4 (2012) [18]
Low-Power	LPDDR3 (2012) [17]; LPDDR4 (2014) [20]
Graphics	GDDR5 (2009) [15]
Performance	eDRAM [28], [32]; RLDRAM3 (2011) [29]
3D-Stacked	WIO (2011) [16]; WIO2 (2014) [21]; MCDRAM (2015) [13]; HBM (2013) [19]; HMC1.0 (2013) [10]; HMC1.1 (2014) [11]
Academic	SBA/SSA (2010) [38]; Staged Reads (2012) [8]; RAIDR (2012) [27]; SALP (2012) [24]; TL-DRAM (2013) [26]; RowClone (2013) [37]; Half-DRAM (2014) [39]; Row-Buffer Decoupling (2014) [33]; SARP (2014) [6]; AL-DRAM (2015) [25]

Table 1. Landscape of DRAM-based memory

Ramulator

- Provides out-of-the box support for many DRAM standards:
  - DDR3/4, LPDDR3/4, GDDR5, WIO1/2, HBM, plus new proposals (SALP, AL-DRAM, TLDRAM, RowClone, and SARP)
- ~2.5X faster than fastest open-source simulator
- Modular and extensible to different standards

Simulator (clang -O3)	*Cycles (10^6)*		*Runtime (sec.)*		*Req/sec (10^3)*		*Memory (MB)*
	Random	*Stream*	*Random*	*Stream*	*Random*	*Stream*	
Ramulator	652	411	752	249	133	402	2.1
DRAMSim2	645	413	2,030	876	49	114	1.2
USIMM	661	409	1,880	750	53	133	4.5
DrSim	647	406	18,109	12,984	6	8	1.6
NVMain	666	413	6,881	5,023	15	20	4,230.0

Table 3. Comparison of five simulators using two traces

Case Study: Comparison of DRAM Standards

Standard	*Rate (MT/s)*	*Timing (CL-RCD-RP)*	*Data-Bus (Width×Chan.)*	*Rank-per-Chan*	*BW (GB/s)*
DDR3	1,600	11-11-11	64-bit × 1	1	11.9
DDR4	2,400	16-16-16	64-bit × 1	1	17.9
SALP†	1,600	11-11-11	64-bit × 1	1	11.9
LPDDR3	1,600	12-15-15	64-bit × 1	1	11.9
LPDDR4	2,400	22-22-22	32-bit × 2*	1	17.9
GDDR5 [12]	6,000	18-18-18	64-bit × 1	1	44.7
HBM	1,000	7-7-7	128-bit × 8*	1	119.2
WIO	266	7-7-7	128-bit × 4*	1	15.9
WIO2	1,066	9-10-10	128-bit × 8*	1	127.2

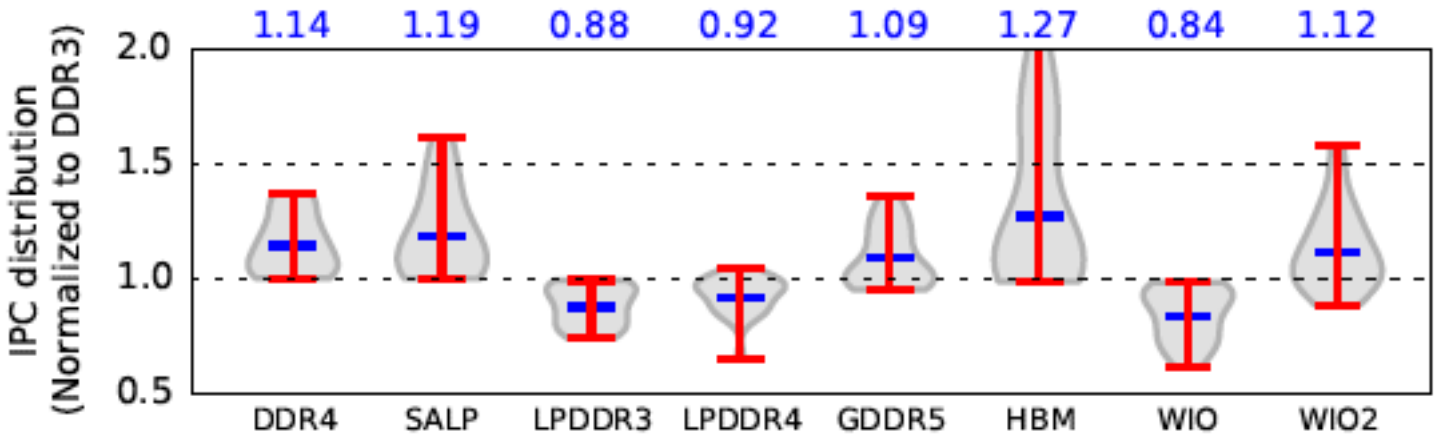


Figure 2. Performance comparison of DRAM standards

Across 22 workloads, simple CPU model

Ramulator Paper and Source Code

- Yoongu Kim, Weikun Yang, and Onur Mutlu,
  "Ramulator: A Fast and Extensible DRAM Simulator"
  IEEE Computer Architecture Letters (***CAL***), March 2015.
  [Source Code]

- Source code is released under the liberal MIT License
  - https://github.com/CMU-SAFARI/ramulator

Ramulator: A Fast and Extensible DRAM Simulator

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Optional Assignment

- Review the Ramulator paper
  - Email me your review
- Download and run Ramulator
  - Compare DDR3, DDR4, SALP, HBM for the libquantum benchmark (provided in Ramulator repository)
  - Email me your report
- This may help you get into memory systems research quickly

End of Backup Slides